

# WP 2 Process Development

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# Work Package 2

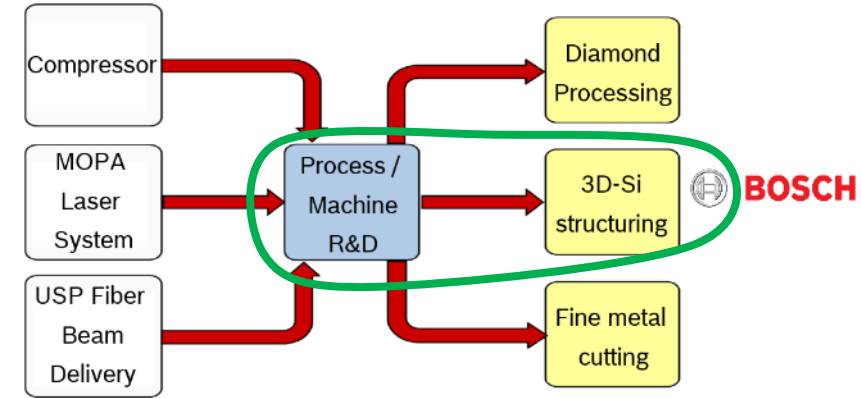
- HIPERDIAS application areas:
  - 3D Silicon processing
  - Fine cutting of metals
  - Diamond ablation
- Agenda:
  - **Task 2.1: Fundamentals Si Processing - Update from Bosch**
  - Task 2.2: Fundamentals Fine Cutting of Metals - Update from C4L
  - Task 2.3: Fundamentals Diamond Ablation – Update from E6
  - Task 2.4: Upscaling – Update from USTUTT

Partners involved:



## HIPERDIAS – BOSCH Objectives

- Overall: physical root-cause analysis ultrashort pulse laser ablation of Si
- WP1: Define characteristic requirements (KPIs)
- WP2.1: Test structure and process evaluation on medium-power systems ( $\cong 50$  W)
- Process optimization & parameter robustness incl.: target specifications HIPERDIAS high-power system (Integration meeting in 05/17 w/ Amplitude, LASEA, USTUTT)
- **WP2.4, WP7: Support process upscaling: Start as soon as IFSW 500 W laser system available**



WP	H1/16	H2/16	H1/17	H2/17	H1/18	H2/18
WP1	Definition and evaluation of KPIs					
WP2.1		Fundamental Process Development & Definition of System Specifications (medium-power lasers up to $\cong 50$ W)				
WP2.4, WP7					Support upscaling to 1 kW system	

completed

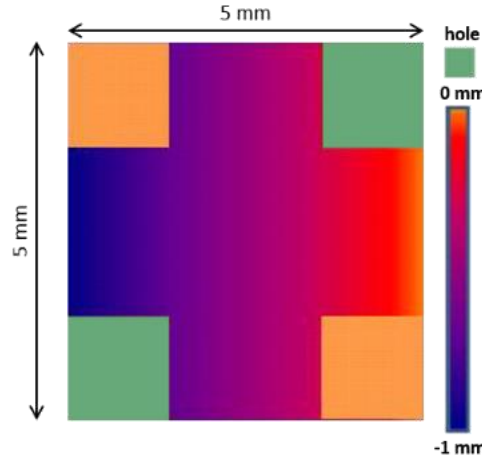
completed

to start asap

## WP 2.1 – BOSCH Key Performance Indicators

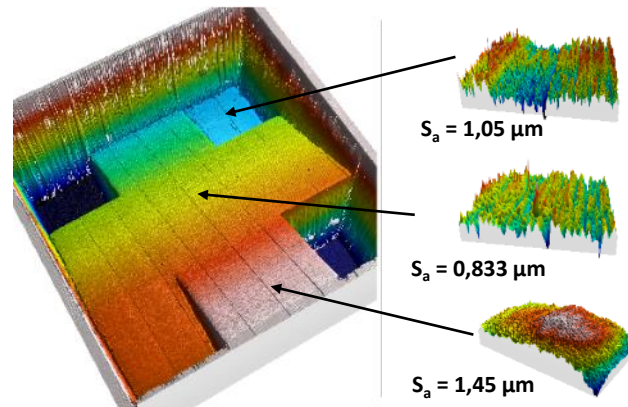
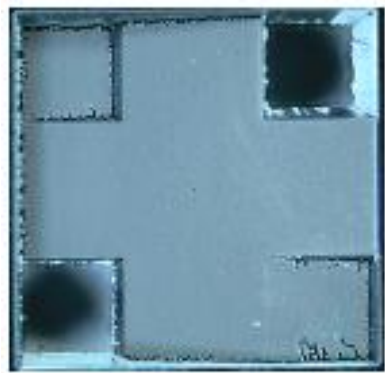
### Test structure

- Features typical of potential applications:
- Ablated volume: 12 mm<sup>3</sup>
- Chamfer
- Steep walls
- Tight radius



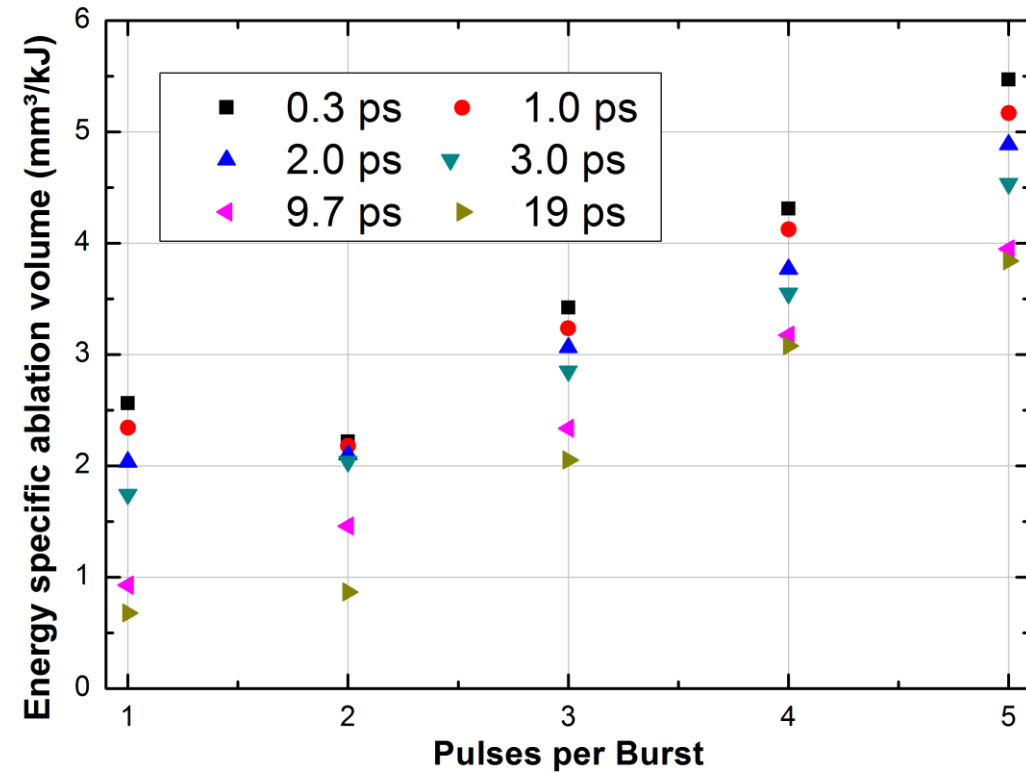
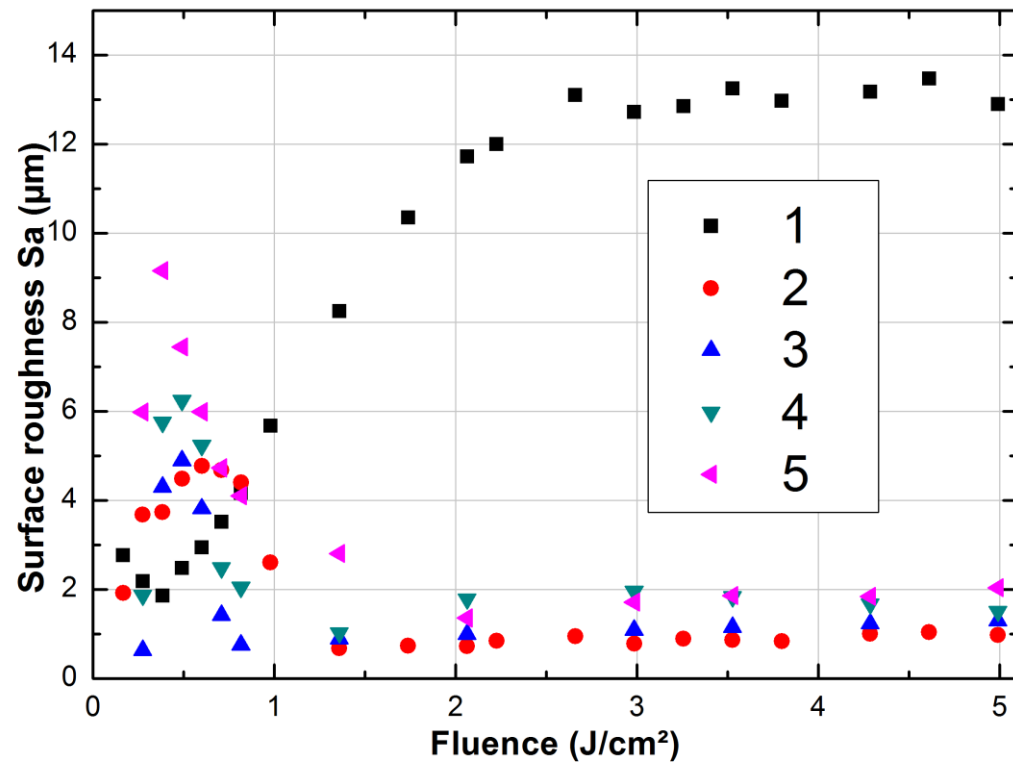
### KPI evaluation

Type	Unit	Target	Current Status
Average ablation rate	mm <sup>3</sup> /s	≥1	0.05
Peak ablation rate	mm <sup>3</sup> /s	≥3	0.1
Average ablation rate (specific)	mm <sup>3</sup> /kJ	≥1	3.1
Peak ablation rate (specific)	mm <sup>3</sup> /kJ	≥3	5.5
Shape deviation	μm	≤10	<10
Average surface roughness Ra	μm	≤1	<0.5
Surface damage thickness	μm	≤1	<1
Surface defects > 1 μm	1/mm <sup>2</sup>	none	None
Min. edge radius	μm	≤ 200	60
Max. edge-steepness	degree	≥ 70	80



- Results achieved: All KPIs w/i specifications, except for absolute ablation rate
- Critical: trade-off between surface quality (roughness) and productivity (ablation rate)
- **Productivity/quality trade-off managed by using burst mode**

## WP 2.1 –Ablation in Burst Mode



**„Sweet spot“ identified w/ 5-pulse bursts, 0.3 ps pulse duration and 2  $\text{J}/\text{cm}^2$  fluence**

## WP 2.1 – Summary

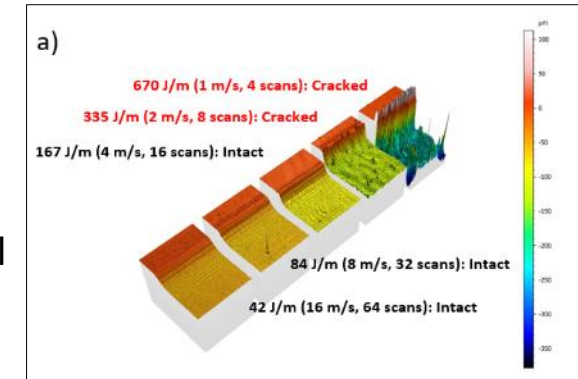
### Single-pulse vs. burst-mode ablation

	single-pulse	2-pulse burst	5-pulse burst
pulse duration to access regime II	> 3 ps	0.3 ps (or less)	0.3 ps (or less)
roughness Ra	$\gg 1\mu\text{m}$ (0.3ps)	1 $\mu\text{m}$	1 $\mu\text{m}$
ablation rate	2.5 mm <sup>3</sup> /kJ	2 mm <sup>3</sup> /kJ	5.5 mm <sup>3</sup> /kJ



### Outlook: Upscaling to 500 W (1000 W)

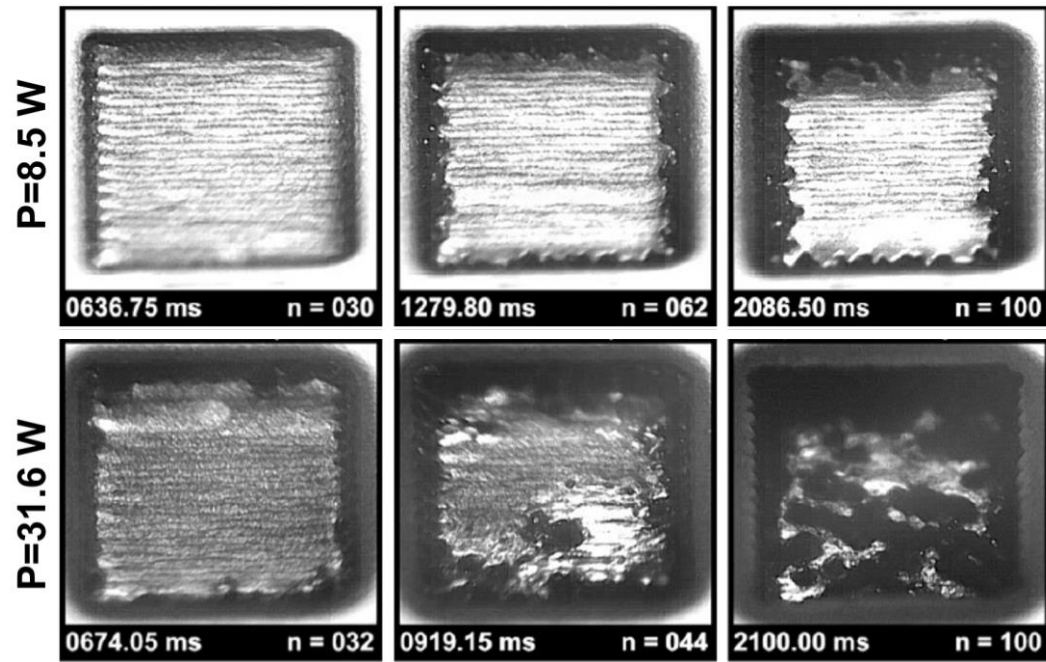
- 1<sup>st</sup> trials w/ 670 W source at USTUTT (2016)
- High scan speed required
- Wafer failure if heat removal insufficient



- System specs defined on integration planning meeting (05/17 at USTUTT)
- Upscaling to start @ USTUTT as soon as laser system available → important challenge:  
**Adapt scanning strategy and heat removal to avoid surface deterioration and catastrophic heat accumulation**

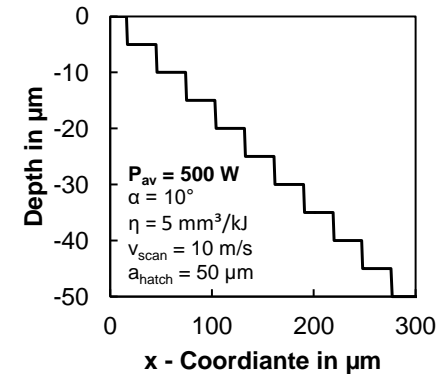
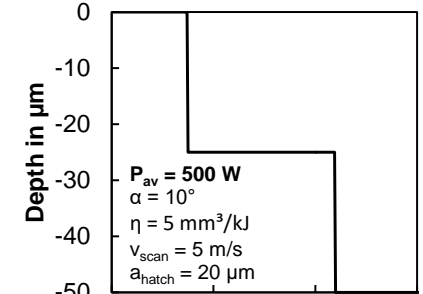
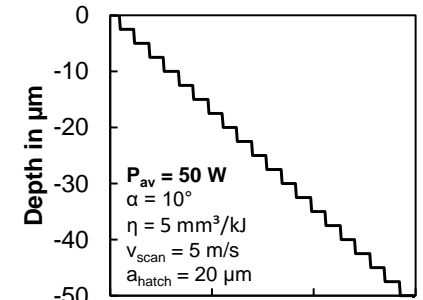


## WP 2.4 – Outlook: Challenges



+ Challenge: Does **higher ablation depth per overscan** interfere with precision requirements?

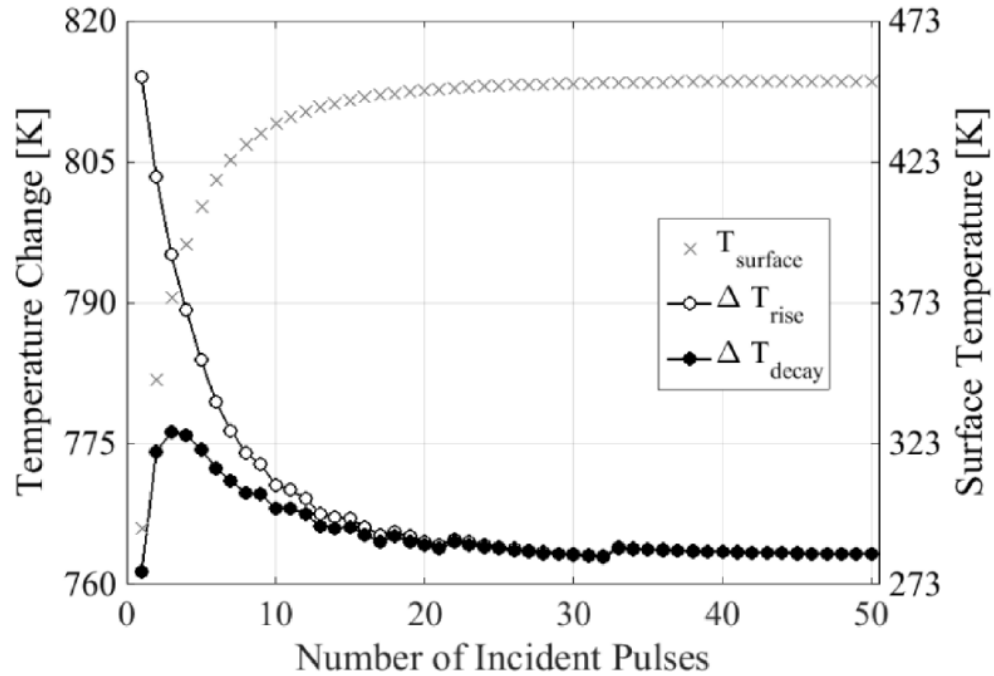
### Geometric impact of parameters on chamfer morphology (example)



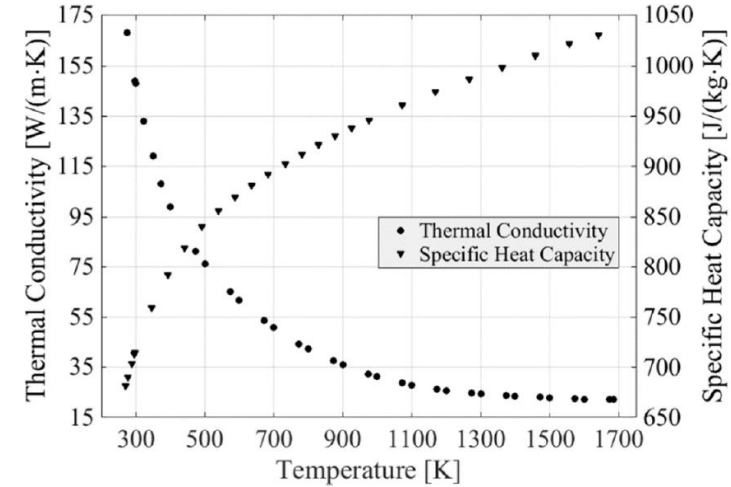
[D. Brinkmeier, Master's thesis]

## WP 2.4 – Outlook: Challenge: Heat Accumulation

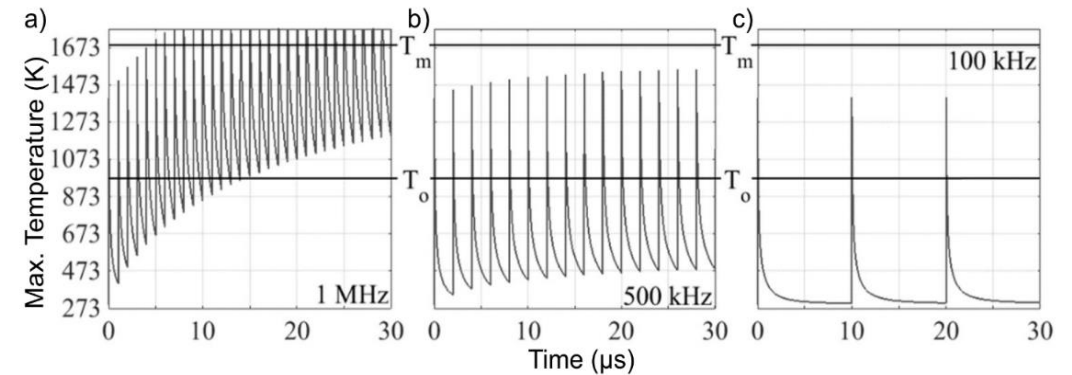
Surface temperature change of wafer due to incident laser pulses



Si material constants as a function of temperature



Evolution of wafer surface temperature during Si ablation at different repetition rates



Taylor, L. L., *et al. Optical Materials Express* **6**:2745

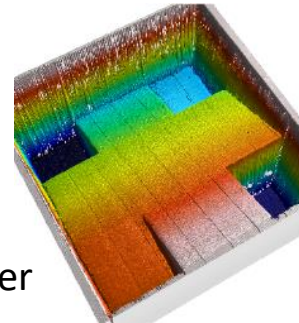


## Bosch Contribution – Current Status

### Milestone M2.1 (M24): **done**

*“High quality 3D Si processing with low average power”*

- KPIs achieved w/ low average power
- Optimum parameter set communicated to laser and system development partners



### Deliverable D2.1 (M24): **done**

- *„Process limits 3D Si processing“*

### Deliverable D2.4 (M30):

- Upscaling Si ablation
- Work to be started asap

# HIPERDIAS

## Deliverable 2.1: Process limits 3D Si processing

**Dissemination Level: Confidential (CO)**

#### Owner

**Name:** Martin Lustfeld  
**Lead Beneficiary:** BOSCH  
**Phone:** +49 1525 8813 570  
**E-mail:** [Martin.lustfeld@de.bosch.com](mailto:Martin.lustfeld@de.bosch.com)

#### Context

**Author(s):** M. Lustfeld, G. Kunz, M. Ametowobla (Bosch); J.A. Ramos de Campos, D. Bruneel (LASEA)  
**Work Package:** WP2  
**Task:** Task 2.1: Fundamental process development 3D Si processing

# Work Package 2

- HIPERDIAS application areas:
  - 3D Silicon processing
  - Fine cutting of metals
  - Diamond ablation
- Agenda:
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  - **Task 2.2: Fundamentals Fine Cutting of Metals - Update from C4L**
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  - Task 2.4: Upscaling – Update from USTUTT

Partners involved:



**BOSCH**



## Description of Work

- **Task 2.2** *Fundamental process development fine cutting of metals* (C4L;USTUTT)
  - Understand process parameters, low power system.
  - Serves as input for upscaling
  - **Completed.** Deliverable 2.2 – M24 (01.2018)
- **Task 2.3** *Fundamental process development diamond ablation* (E6; C4L)
  - Support role for E6, facilitate experimentation.
  - **Completed.** Deliverable 2.3 – M24 (01.2018)
- **Task 2.4** *Upscaling of applications for high throughput* (USTUTT; C4L,BOSCH,LASEA)
  - Achieve KPI's
  - **Incomplete.** Deliverable 2.5 – M30, Deliverable 2.6 – M30 (07.2018)

# WP 2 – Deliverables

Deliverable	Title	Due Date	Status	Update
D2.1	D2.1 Process limits 3D Si processing	M24 (01.2018)	✓	
D2.2	D2.2 Process limits fine cutting of metal	M24 (01.2018)	✓	
D2.3	D2.3 Process limits diamond processing	M24 (01.2018)	✓	
D2.4	D2.4 Processing strategies for high power 3D Si processing	M30 (07.2018)		
D2.5	D2.5 Processing strategies for high power fine cutting of metal	M30 (07.2018)	✗	M36 (01.2019)
D2.6	D2.6 Processing strategies for high power diamond processing	M30 (07.2018)	✗	M36 (01.2019)

# Deliverable 2.2 – Set up

## Laser Source: Carbide (Light Conversion)

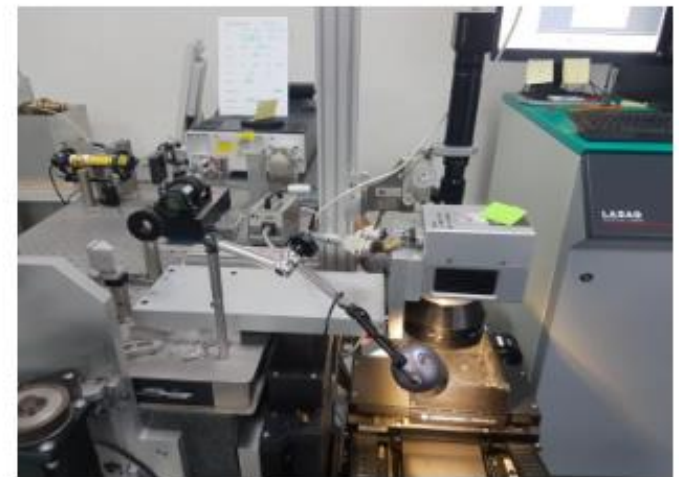
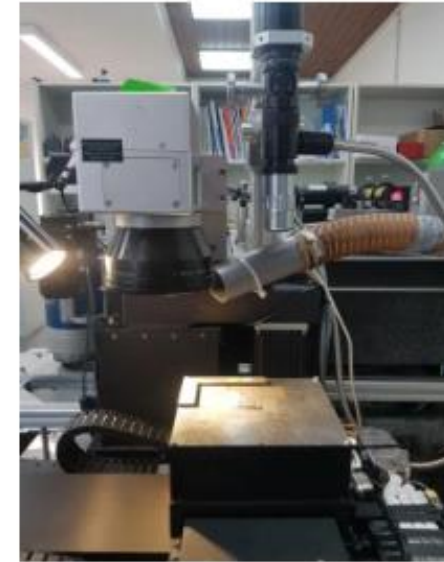
Wavelength	1030nm
Average power	5 W
Max. pulse energy	83 $\mu$ J
Max. frequency	1 MHz
Pulse duration	230 fs to 20 ps

## Beam deflection : Scancube III 14 (Scanlab)

Operation	Galvanometer
Marking speed	2500 mm.s <sup>-1</sup>
Scan field	70mm <sup>2</sup> (100mm telecentric)

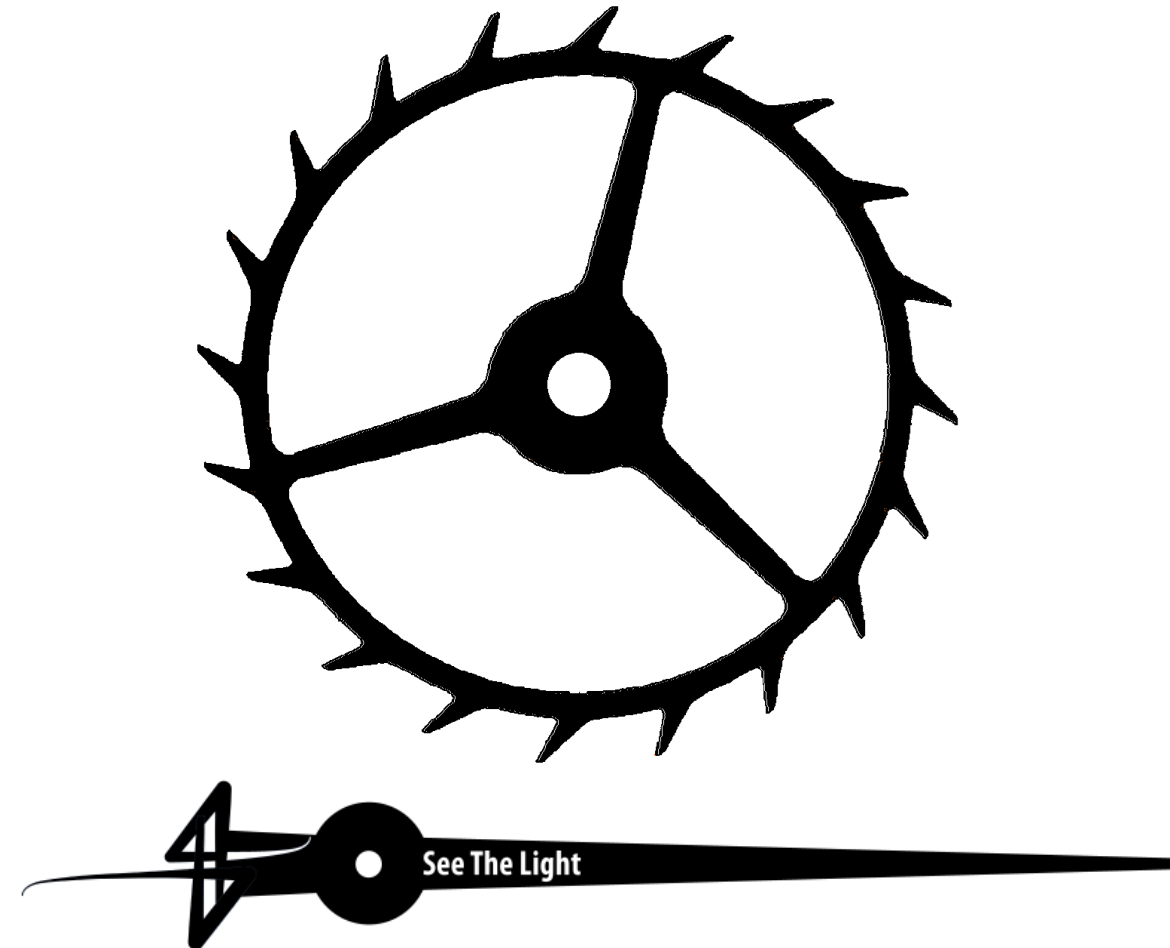
## Axis : PRO165LM (Aerotech)

Axis	X,Y,Z
Repeatability	< 1 $\mu$ m
Accuracy	2 $\mu$ m
Max speed	2000 mm.s <sup>-1</sup>



# Deliverable 2.2 – Material

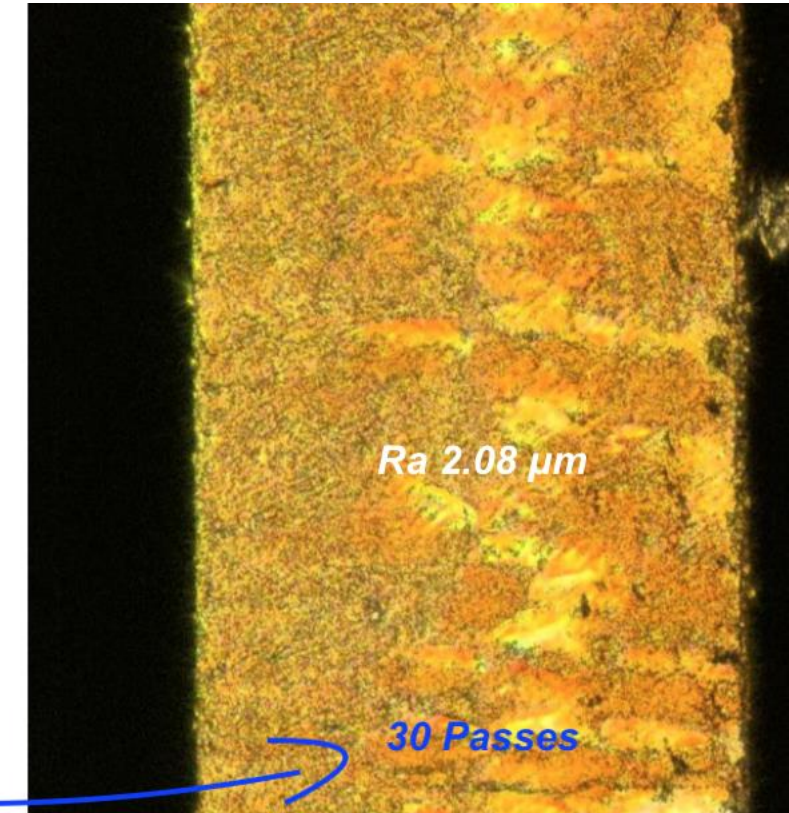
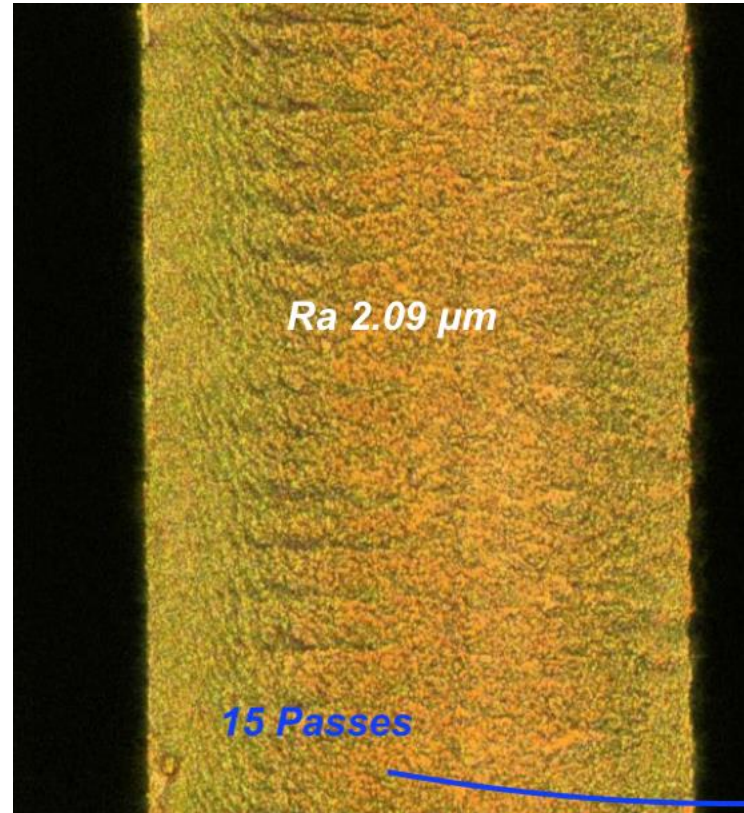
<b>Brass :</b>	MS63 (Allmeson GmbH)
	Cu:Zn                    63:37
	Thickness                0.2 mm
	Geometry                 Variable
	Density                    8.5g.cm <sup>-3</sup>
	Melting Point            920°C
<b>Steel :</b>	1.4310 (Deutsche Edelstahlwerke)
	Contents                  Fe, Cr, Ni, Mn, Mo, N, C, P, S, Si
	Thickness                0.2 mm
	Density                    7.9 g.cm <sup>-3</sup>
	Melting Point            1420 °C
	Geometry                 Variable
	Characteristics          Good mechanical, high tensile strength suitable



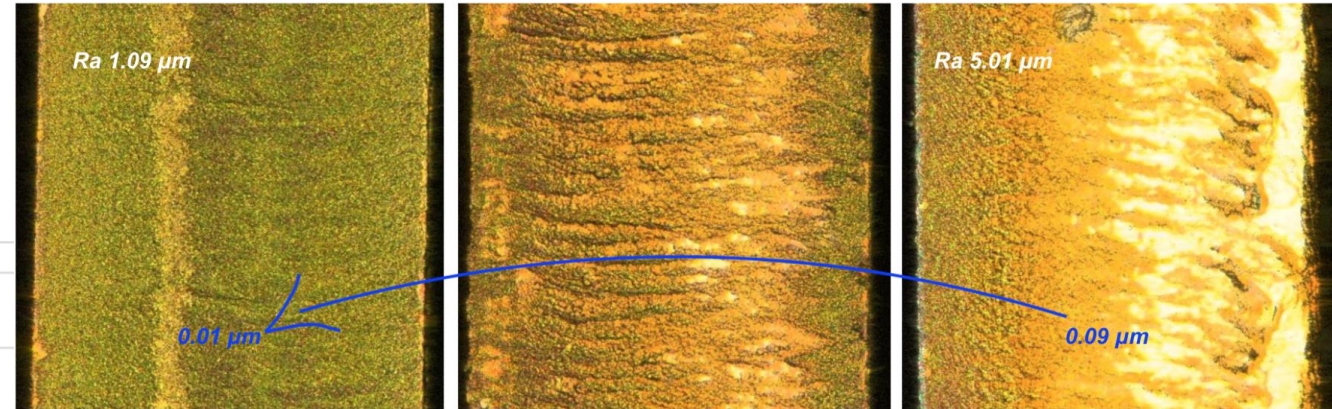
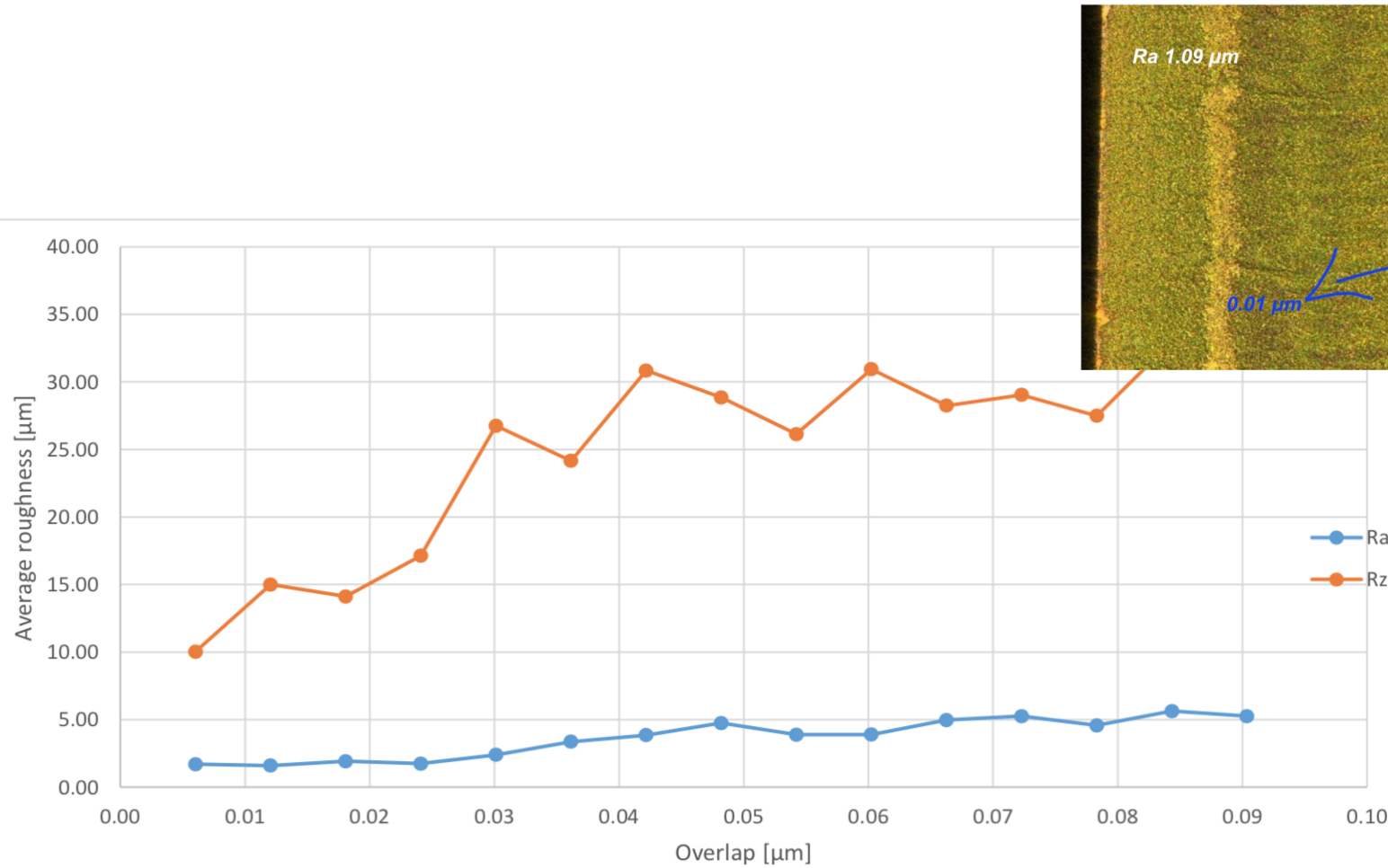


# Deliverable 2.2 – Conclusions

- Visual inspection must be used, equal consideration.
- Recalibration for 120W system trials



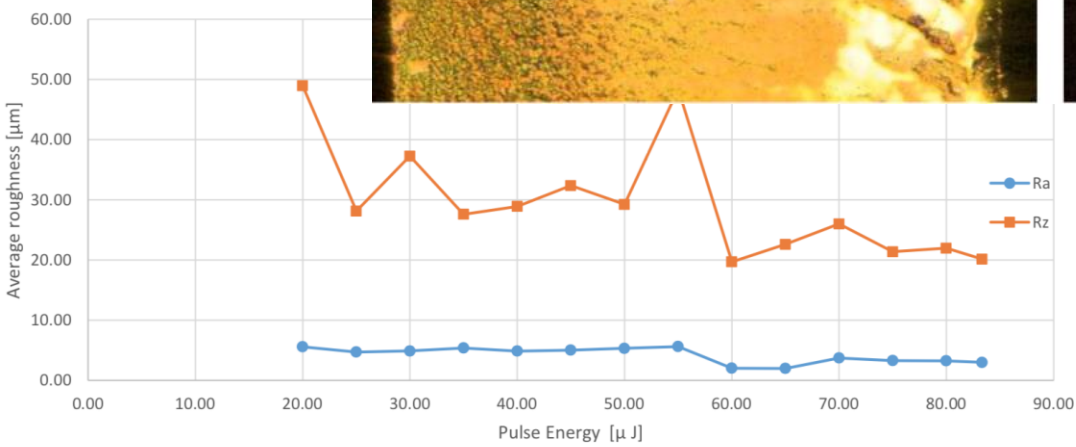
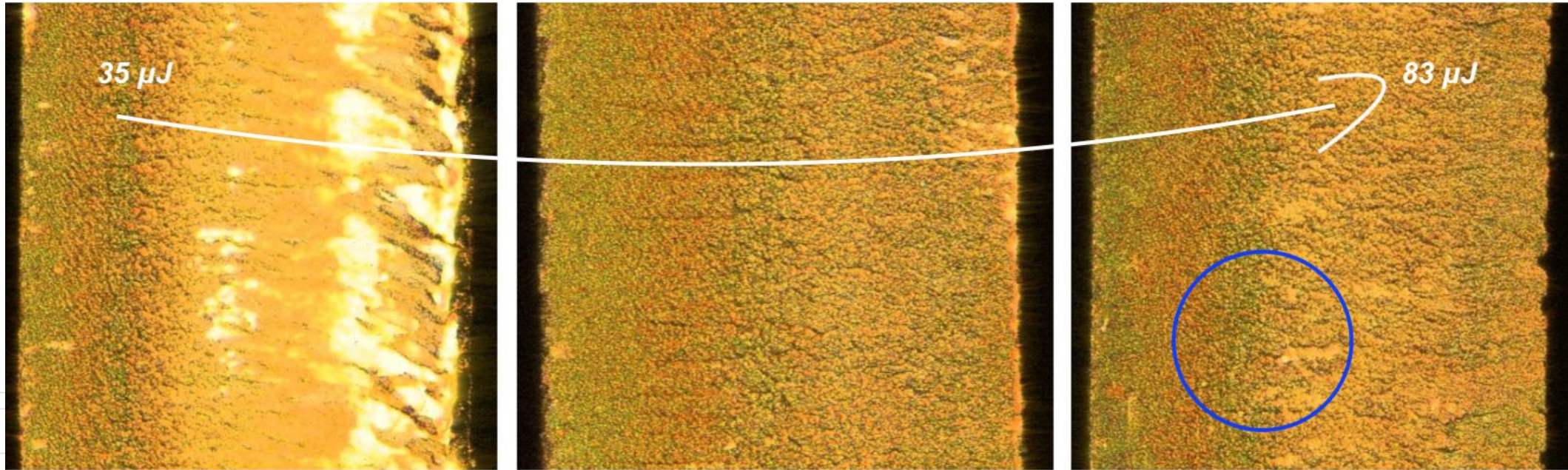
## Deliverable 2.2 – Conclusions



- Overlap minimized
- Slow speeds 6 – 90 mm.min<sup>-1</sup>
- 30.12 µJ, 166kHz



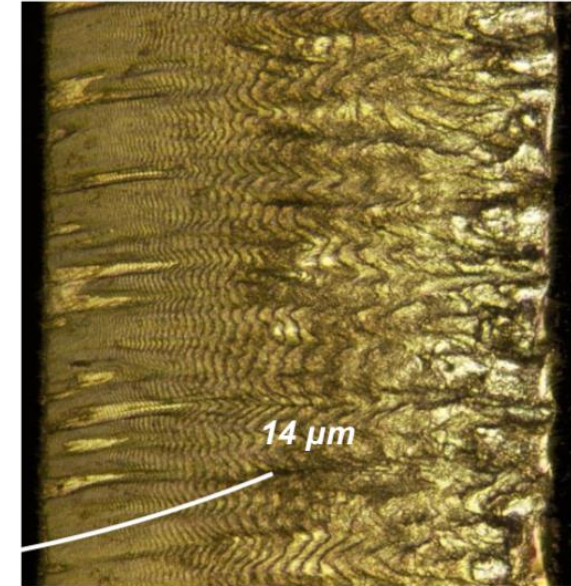
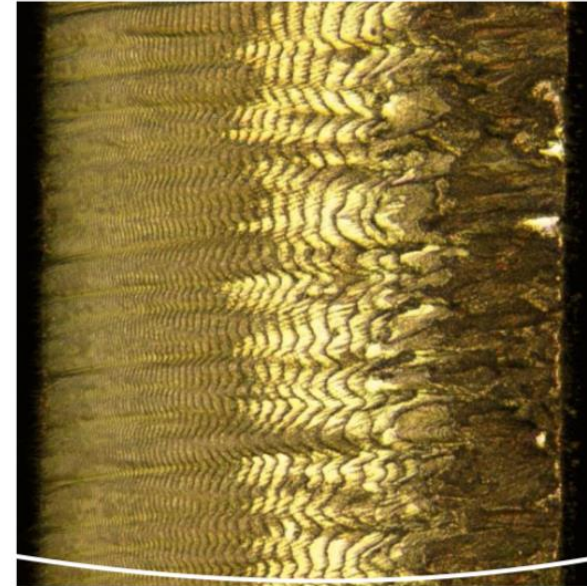
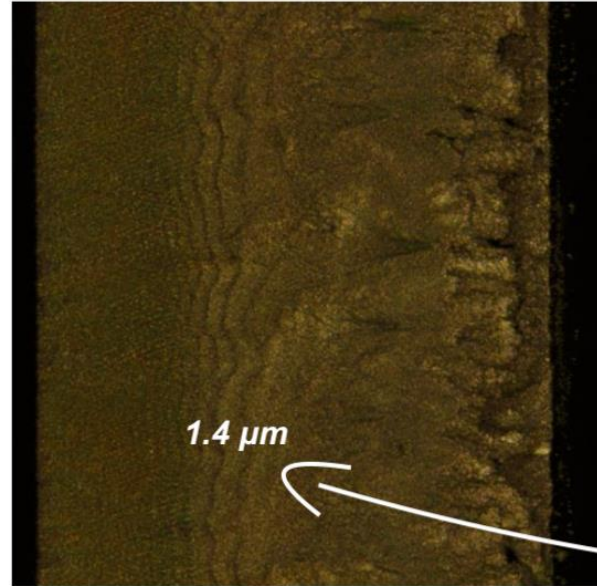
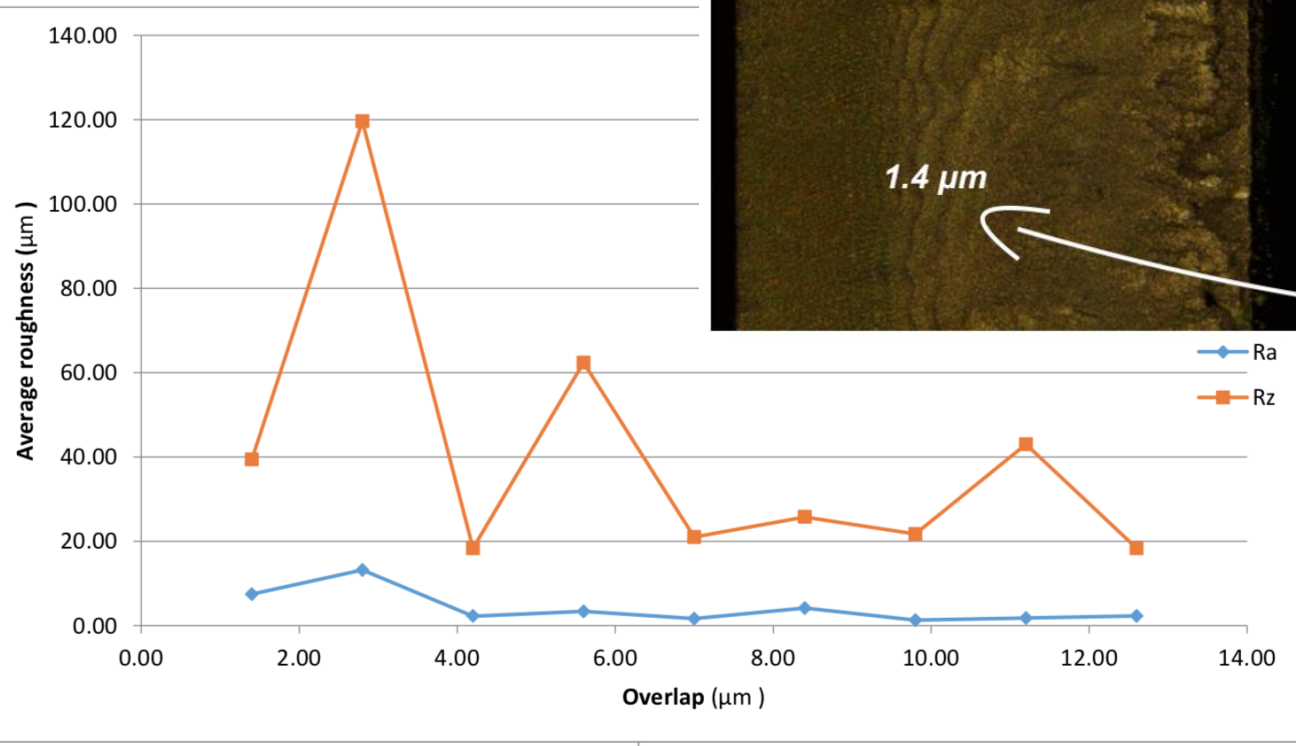
## Deliverable 2.2 – Conclusions



- More pulse energy
- 37.5 mm/min
- 0.09 μm Overlap

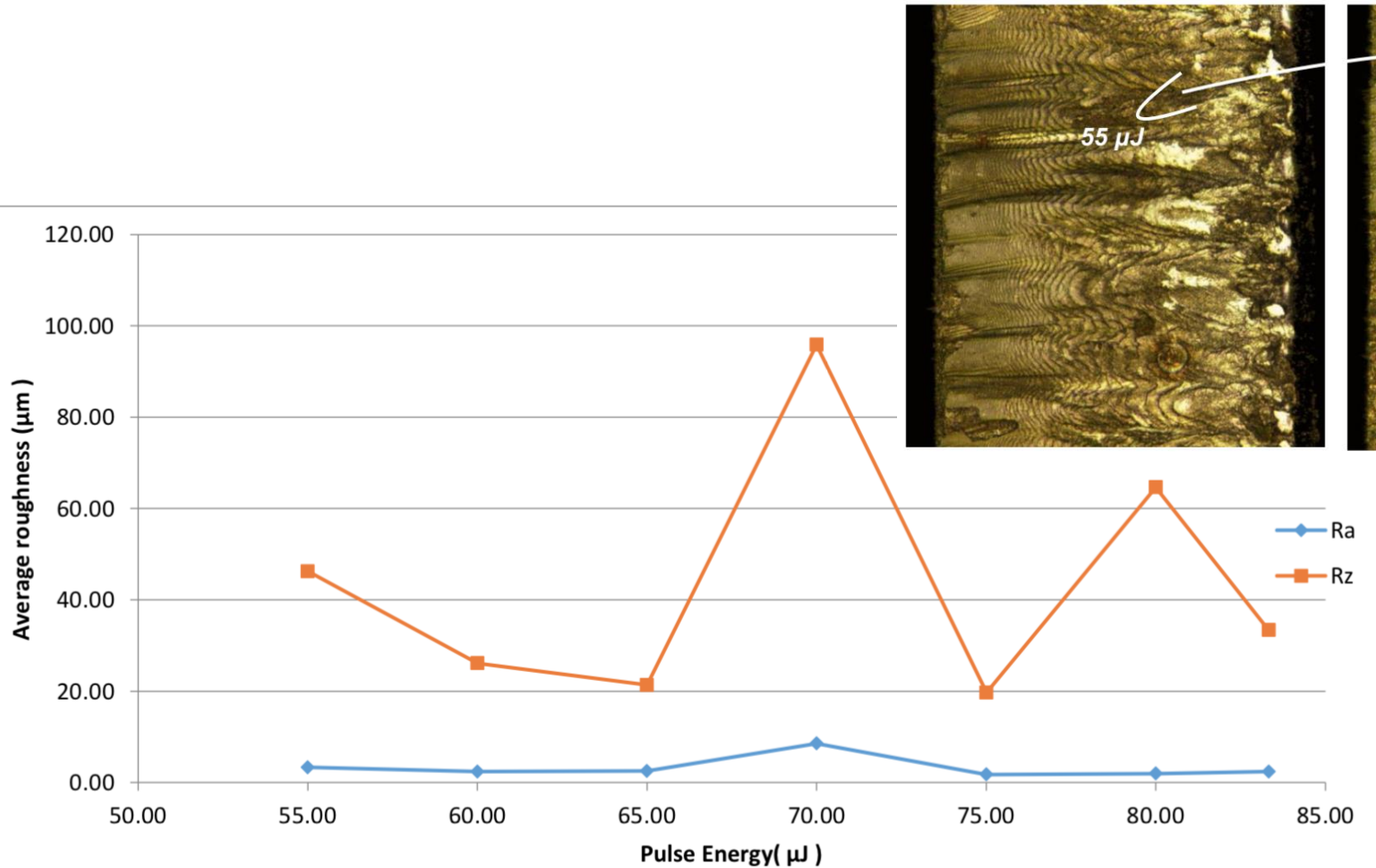


## Deliverable 2.2 – Conclusions



- 70 μl
- 400fs
- 71 kHz
- 33 mm.min<sup>-1</sup>

## Deliverable 2.2 – Conclusions



- 400 fs
- 60 kHz
- 8.33 µm Overlap
- 23 - 43 mm.min<sup>-1</sup>



# WP 2 Plan of experimentation

2 Step process

2 Months – Primary processing  
(fundamental process development)

3 Months – Applied processing

1 Month – Buffer

No.	KPI	Values	Validation status
1	Cutting speed	Expected : $\geq 400$ mm/min	●
		Validated : $\geq 300$ mm /min	●
		Not validated : $< 300$ mm/min	●
2	Post Processing/Cleaning	Expected : Washing	●
		Validated : Vibratory grinding (electro-polishing for some parts only)	●
		Not validated : Additional work/cost	●
3	Production Cost <i>In €, for 1 watch arm 0.15mm thick – 20mm long – batch of 1000</i>	Expected : $\leq 0.4$	●
		Validated : $\leq 0.45$	●
		Non validated : $> 0.45$	●
4	Surface roughness (functional/non-functional)	Validated : $\geq 300$ mm /min	●
		Not validated : $< 300$ mm/min	●
		Not validated : $R_a \geq 1 \mu\text{m}$	●
5	Shape deviation	Expected : $< \pm 2 \mu\text{m}$	●
		Validated : $< \pm 5 \mu\text{m}$	●
		Not validated : $> \pm 5 \mu\text{m}$	●
6	Taper	Expected : $0^\circ$	●
		Validated : Within dimension tolerances	●
		Not validated : Above dimension tolerances	●
7	Colouration	Expected : None	●
		Validated : Washable surface oxidation	●
		Not validated : Persistent surface oxidation	●
8	Untying of part	Expected : Fall down in US-bath	●
		Validated : Fall down in US-bath with separation cut	●
		Not validated : Mechanical removal	●



# WP 2 *Process development*

Task	M23	M24	M25	M26	M27	M28	M29	M30	M31	M32	M33	M34
<b>Fundamental developmetn (5W)</b>	D2.2											
<b>Laser arrival</b>						May (Mid)		July (Mid)				
<b>Upscaled applications</b>												
<b>Fundamental processing (120W)</b>										Sep (Mid)		
<b>Applied Processing (120W)</b>										Sep (Mid)		→ Jan (Mid)
<b>4 beam path processing</b>								July (Late)				

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  - **Task 2.3: Fundamentals Diamond Ablation – Update from E6**
  - Task 2.4: Upscaling – Update from USTUTT

Partners involved:



# Task 2.3: Fundamental process development diamond ablation

- Status

- T2.3

Complete ✓

- D2.3 confidential version

Document complete ✓

- D2.3 public version

Awaiting for approval from engineering manager ✓

# Task 2.3: Fundamental process development diamond ablation

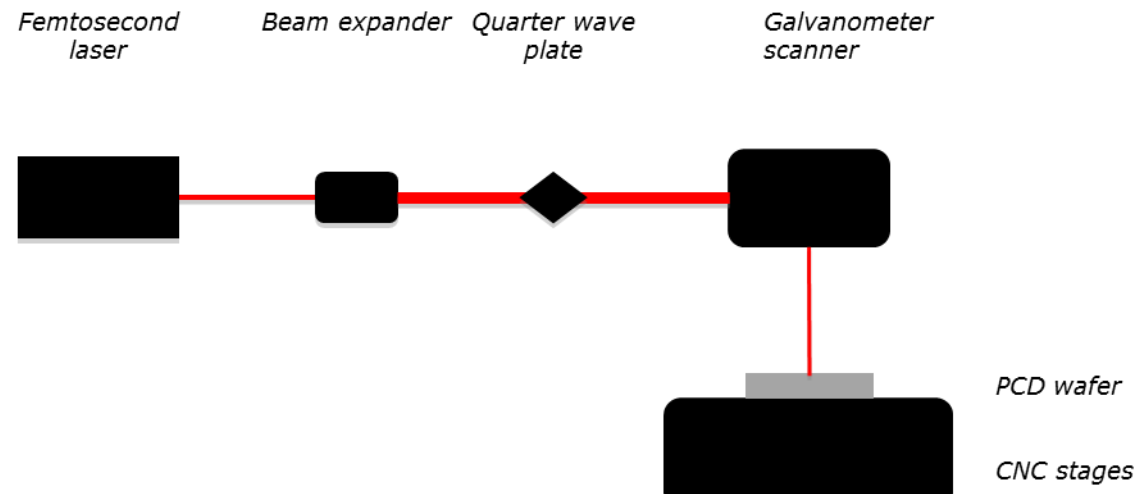
- Experimental set up
  - Three Element Six PCD grades tested

PCD Grade Name	Average Grain Size ( $\mu\text{m}$ )	Diamond Content (wt %)	Cobalt Content (wt%)
CMX850	1	80	20
CTB010	12	90	10
CTM025	30	90	10

- Grades presenting highest variation in diamond grain size and diamond content

# Task 2.3: Fundamental process development diamond ablation

- Experimental set up
  - Ablation trials with low power ultra-short pulsed laser

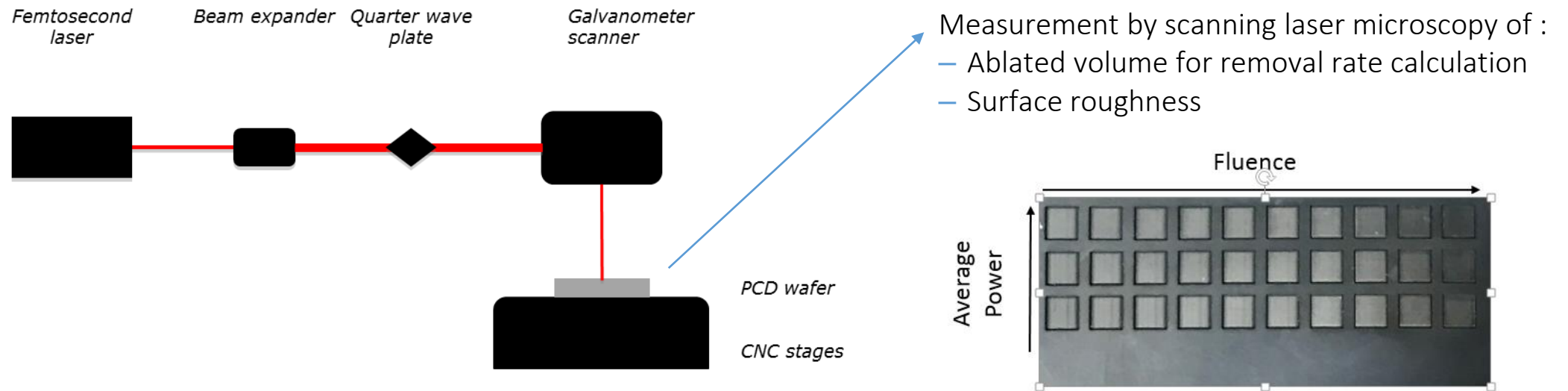


Characteristics of the femtosecond laser used in T2.3:

Wavelength	1030nm
Pulse length	230fs – 10ps
Maximum average power	5W
Frequency	60kHz – 1MHz
Polarization	Linear
M <sup>2</sup>	< 1.2

# Task 2.3: Fundamental process development diamond ablation

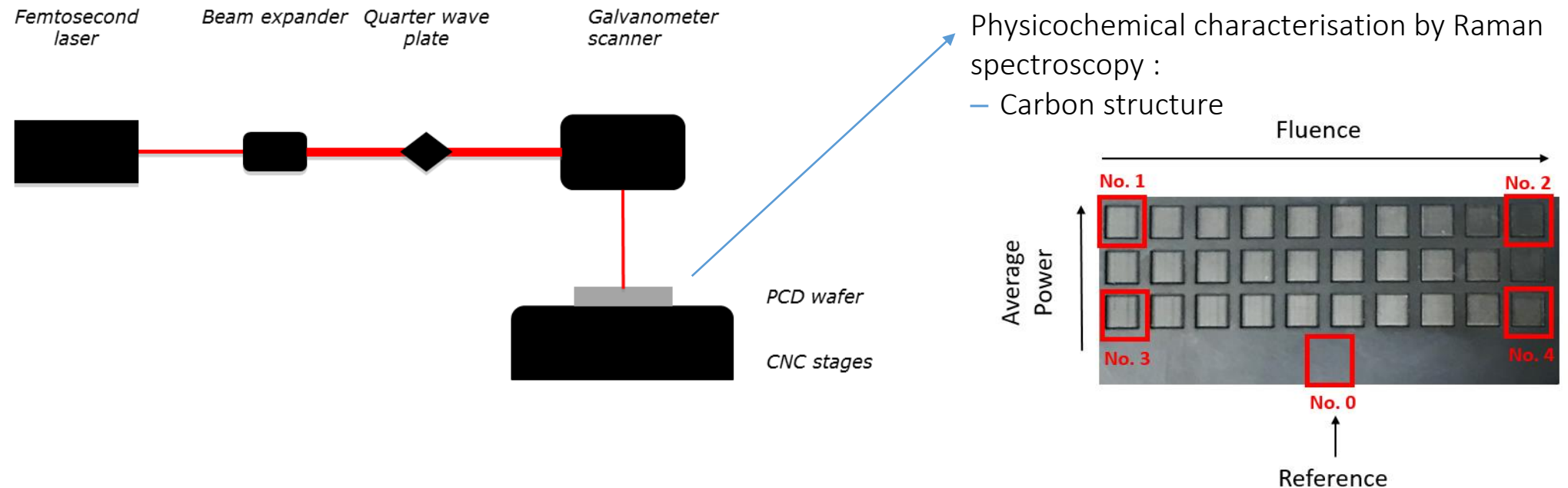
- Experimental Set Up
  - Ablation trials with low power ultra-short pulsed laser





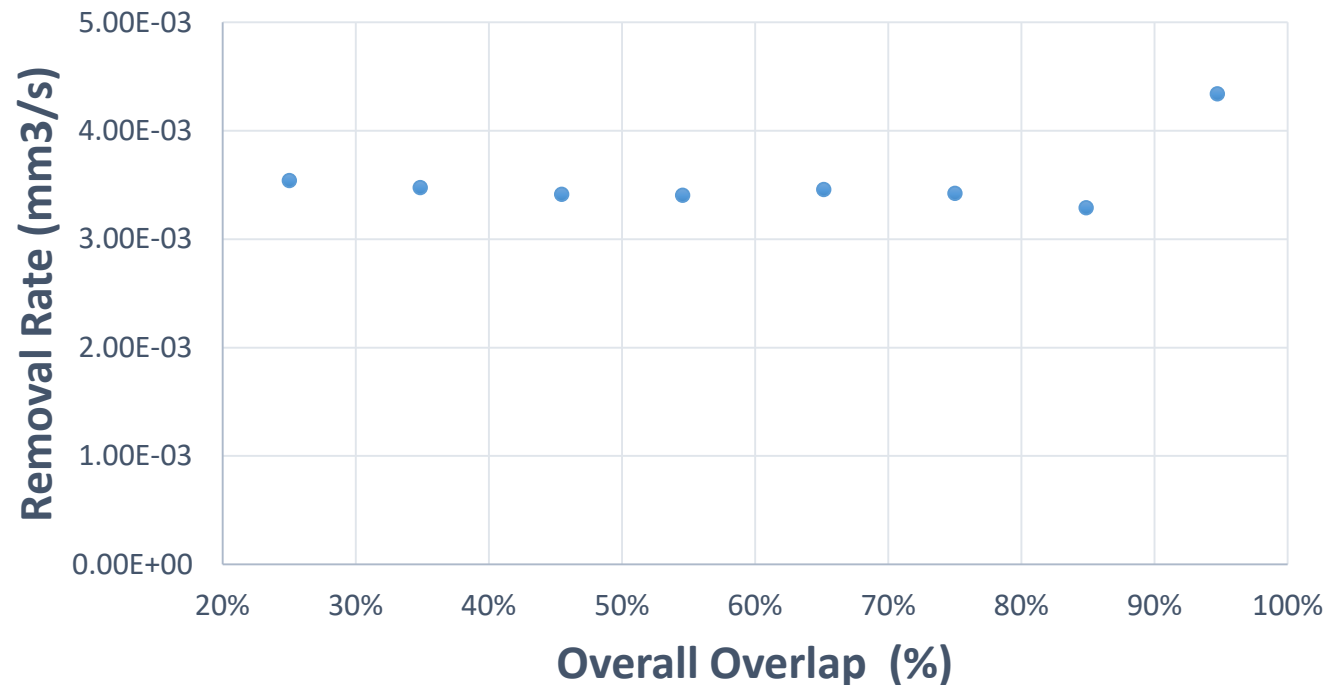
# Task 2.3: Fundamental process development diamond ablation

- Experimental Set Up
  - Ablation trials with low power ultra-short pulsed laser



# Task 2.3: Fundamental process development diamond ablation

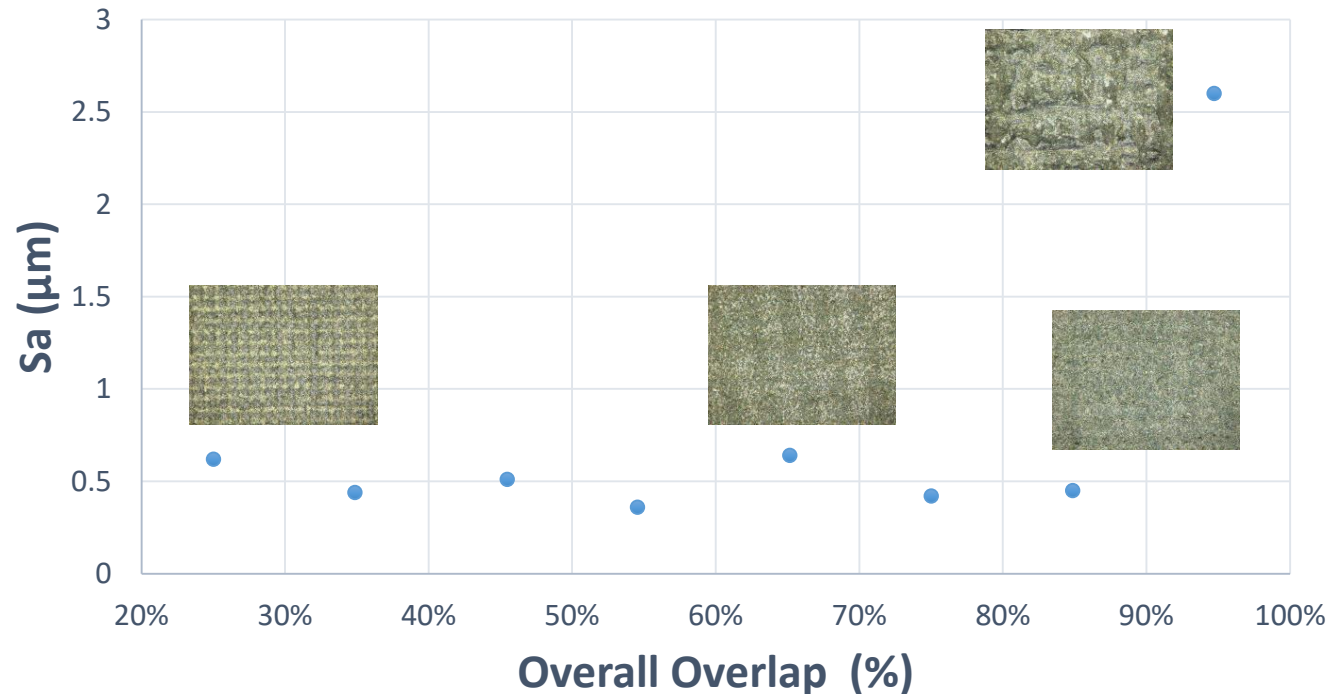
- Influence of Heat Accumulation
  - Increase of ablation rate with heat accumulation



Over 95% overlap :  
— Increase of ablation rate

# Task 2.3: Fundamental process development diamond ablation

- Influence of Heat Accumulation
  - Increase of ablation rate with heat accumulation



Over 95% overlap :  
 — Increase of ablation rate  
 — Surface critically damaged

**HEAT ACCUMULATION EFFECT**

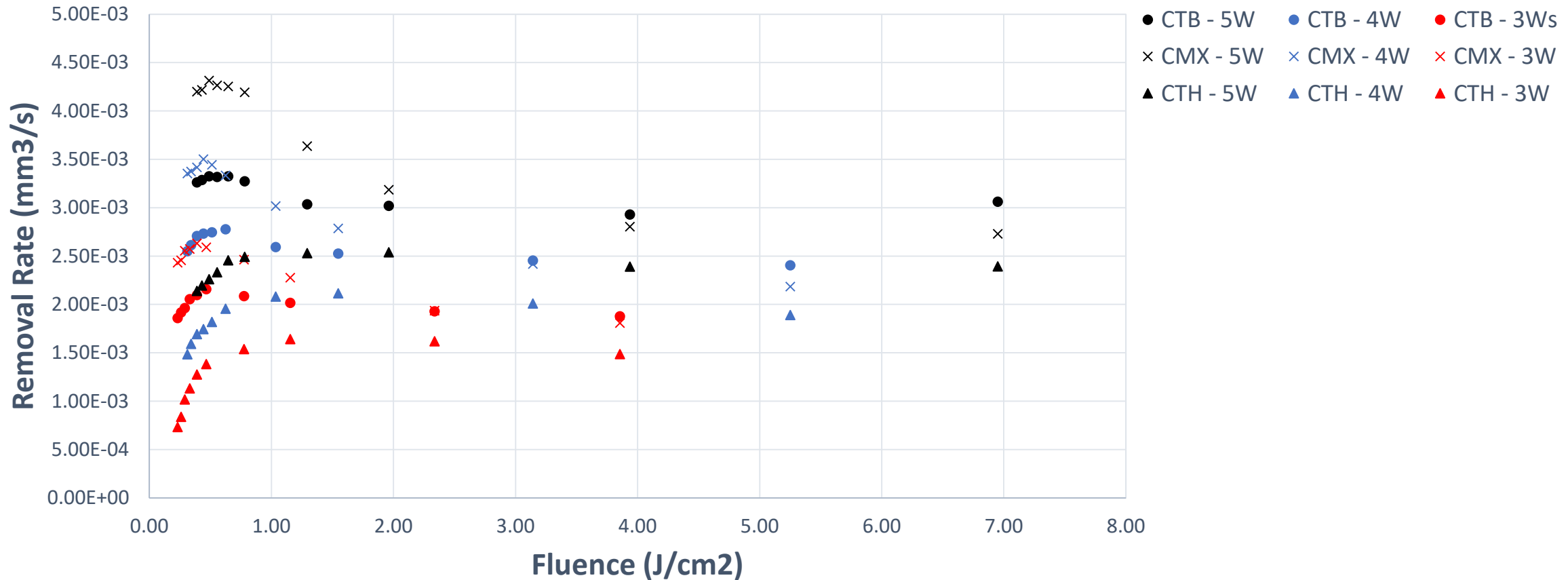
# Task 2.3: Fundamental process development diamond ablation

- Variation of Ablation Rate with PCD grades
  - PCD grades

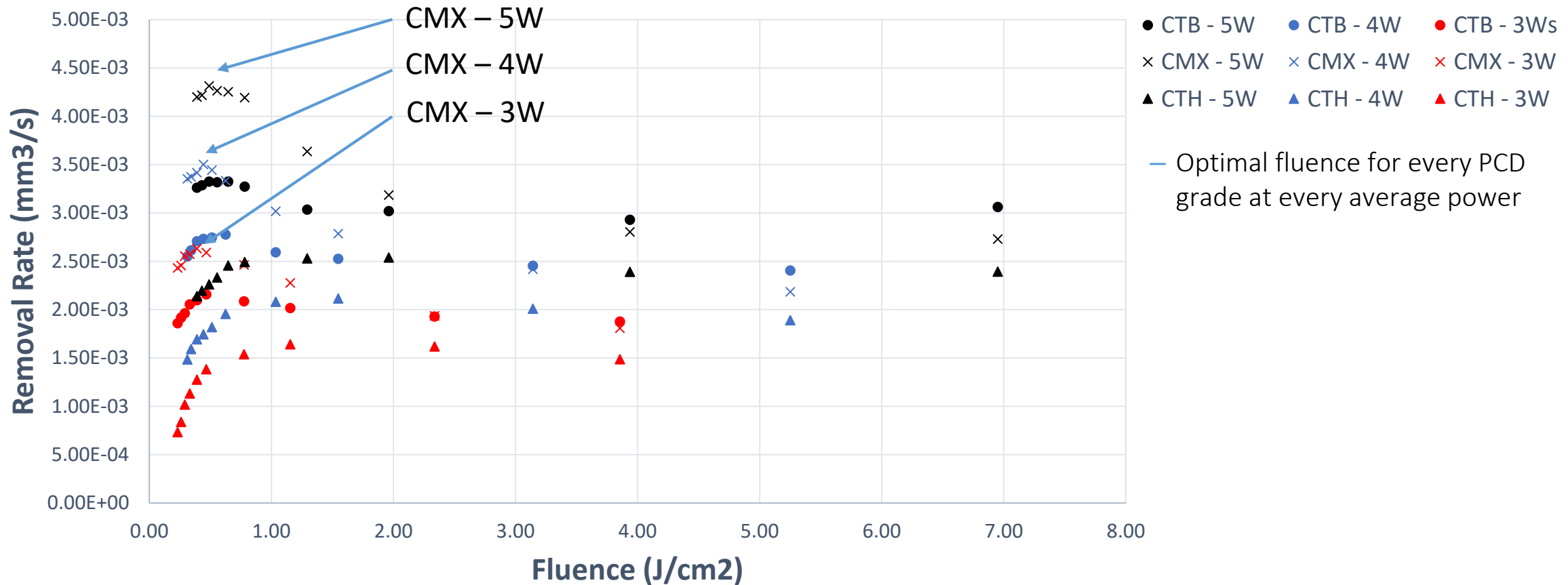
PCD Grade Name	Average Grain Size (µm)	Diamond Content (wt %)	Cobalt Content (wt%)
CMX850	1	80	20
CTB010	12	90	10
CTM025	30	90	10

- Measurement of the ablation rate variation with fluence

# Task 2.3: Fundamental process development diamond ablation

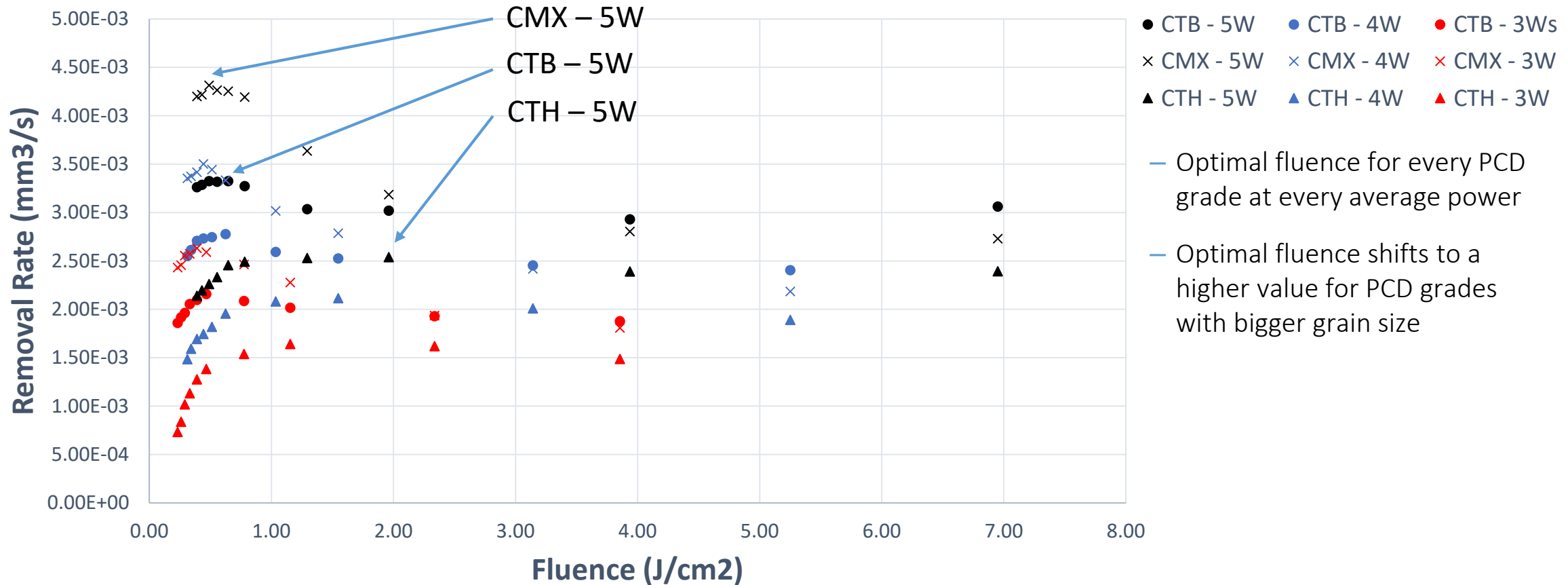


## Task 2.3: Fundamental process development diamond ablation

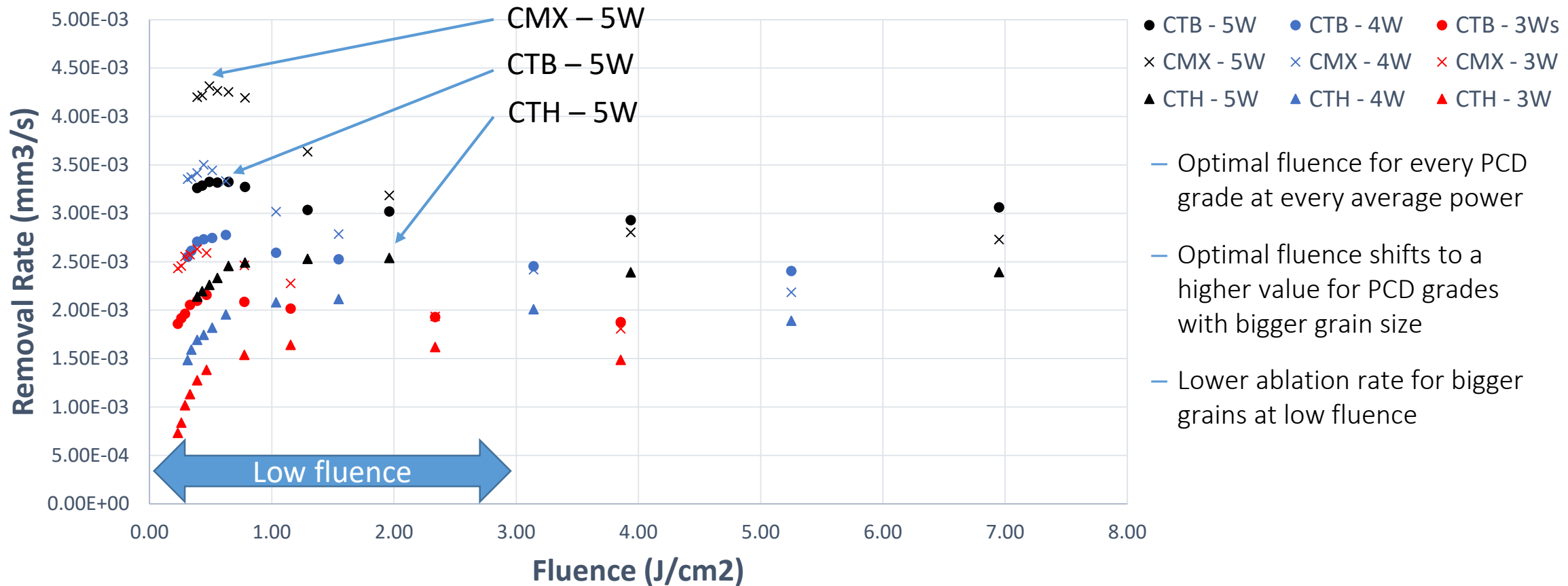




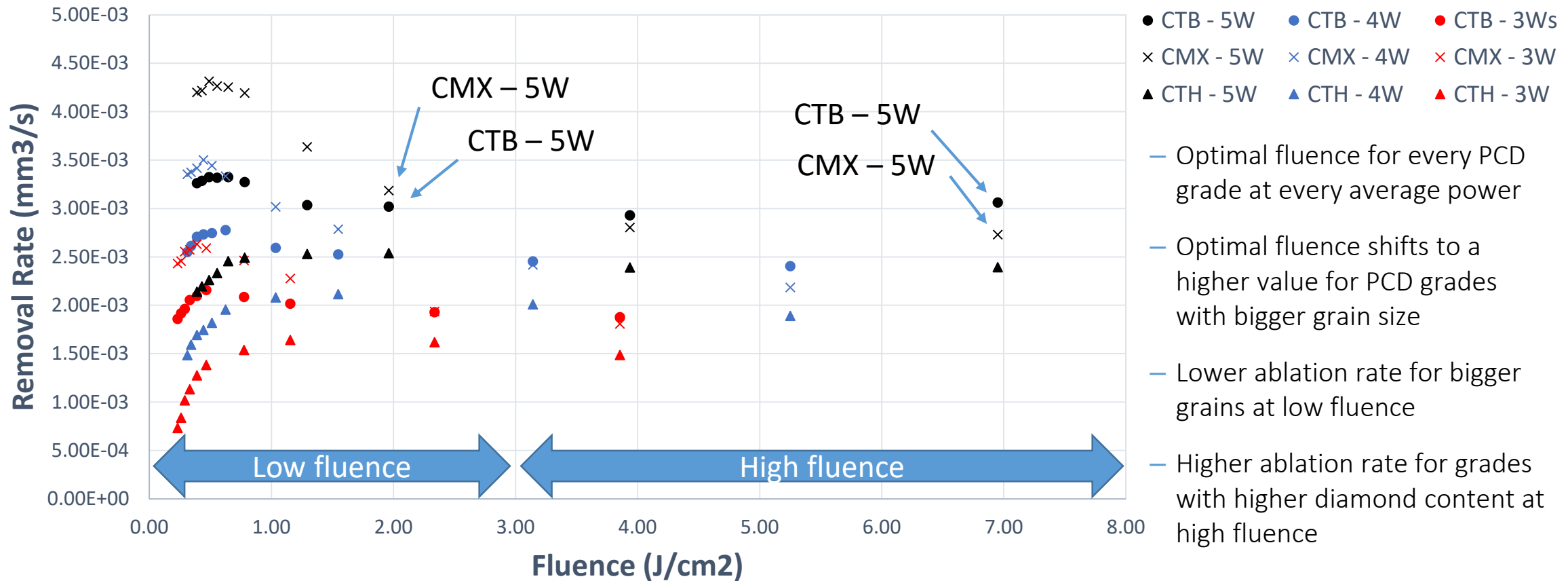
## Task 2.3: Fundamental process development diamond ablation



## Task 2.3: Fundamental process development diamond ablation



## Task 2.3: Fundamental process development diamond ablation



# Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
  - Two steps processing
    - Polishing to be achieved with spot size below 10 $\mu$ m
    - Optimal fluence expected between 0.5J/cm<sup>-2</sup> and 1J/cm<sup>-2</sup> for processing at high power
    - High power laser over 100 $\mu$ J pulse energy
    - Fluence over 1J/cm<sup>-2</sup> with 100 $\mu$ J and spot of 10 $\mu$ m
    - So two processing steps required:
      1. Smoothing step will be performed with large spot size at high pulse energy/high average power
      2. Finishing step will be performed with small spot at low pulse energy/low average power

# Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
  - Maximum spot size

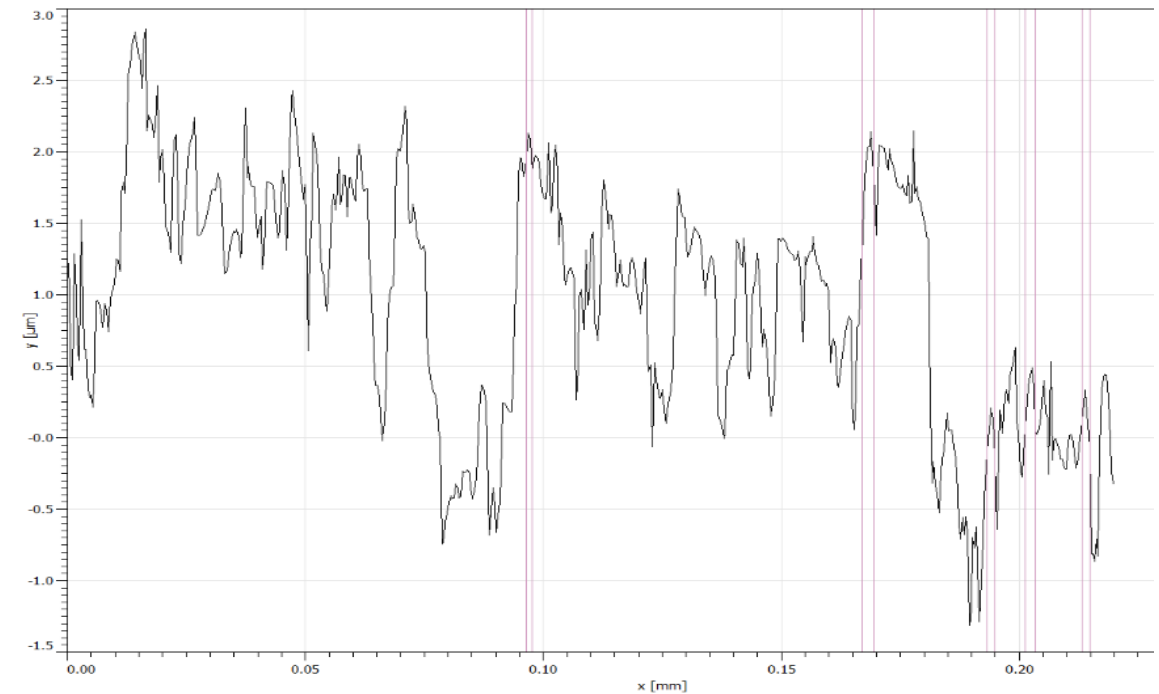
$$d = 2 \sqrt{\frac{E}{\pi F}}$$

Average power:  $P = 200\text{W}$   
 Frequency:  $f = 2\text{MHz}$   
 Pulse energy:  $E = 100\mu\text{J}$

Optimal fluence: $F =$	<b>0.49J/cm<sup>-2</sup></b>	<b>1J/cm<sup>-2</sup></b>	<b>2J/cm<sup>-2</sup></b>
Spot diameter: $d =$	<b>160μm</b> <b>Maximal spot size</b>	112μm	80μm

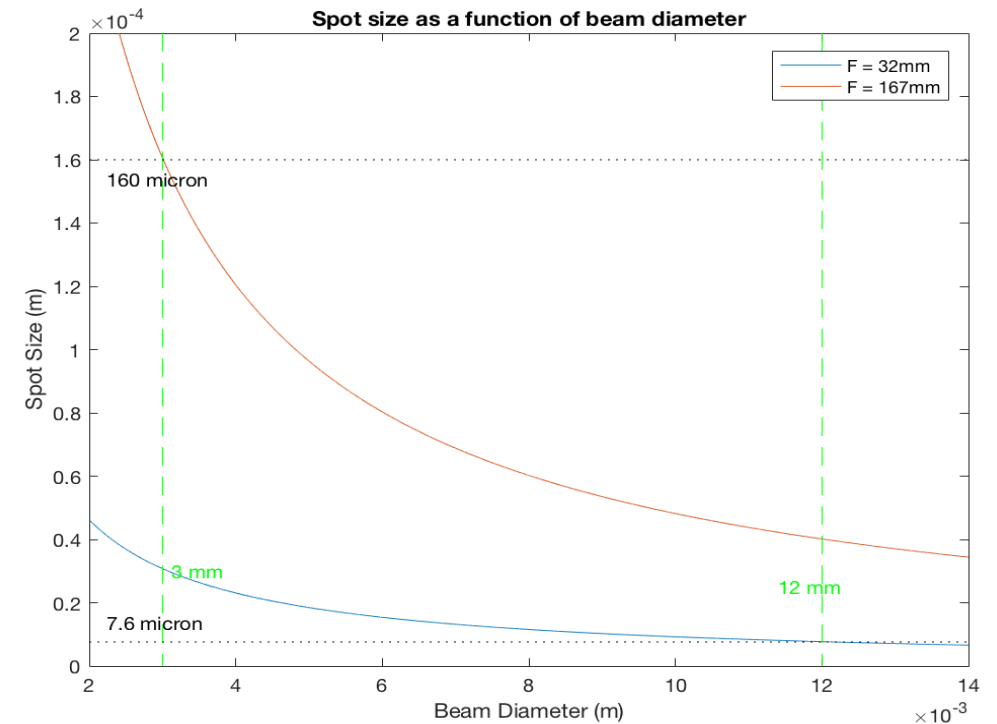
# Task 2.3: Fundamental process development diamond ablation

- Process Optimization and Limitation in Spot Size
  - Minimum spot size
    - Topography of lapped PCD wafer
    - Peak with an average width of  $1\mu\text{m}$
    - Optimal minimum spot size  $1\mu\text{m}$
    - Not corresponding to final ablated surface prior to laser-polishing



# Task 2.3: Fundamental process development diamond ablation

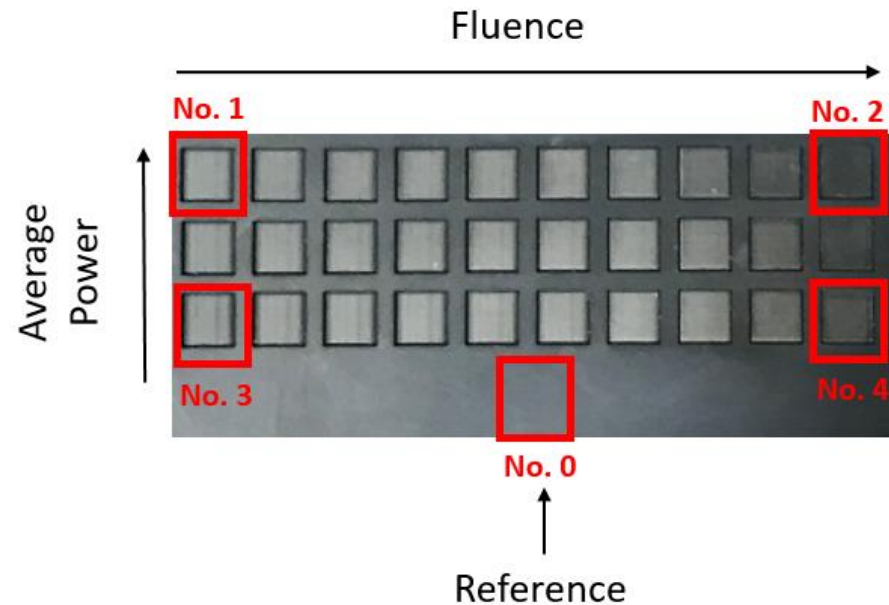
- Process Optimization and Limitation in Spot Size
  - Limitation in spot size and speed
    - Minimum can only reach 7.6 $\mu\text{m}$ .  
Not critical as topography after ablation at high power is yet unknown.  
The goal was to determine smallest spot achievable on this system.
    - Maximum reaches 160 $\mu\text{m}$ .  
Match the requirement of spot diameter to work close to the optimal fluence at high pulse energy





# Task 2.3: Fundamental process development diamond ablation

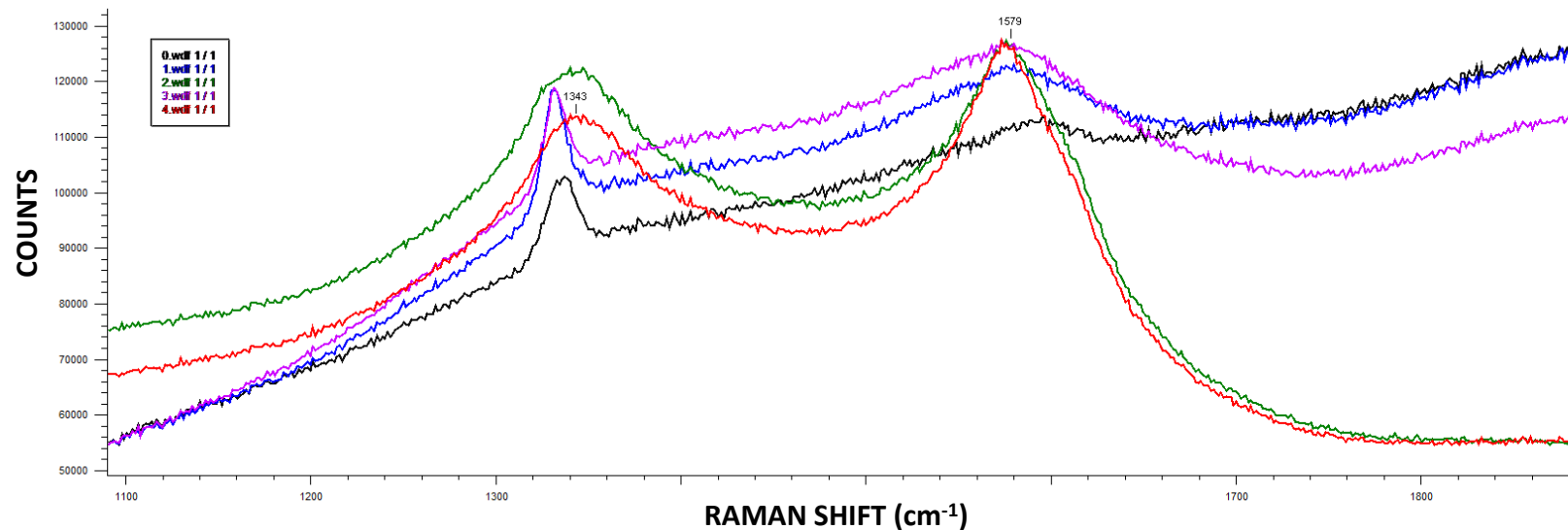
- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - Raman spectroscopy analyses



<b>Area 0</b>	Reference point (initial surface)	Lapped surface for CMX850* EDM ground surface for CTB010*
<b>Sample 1</b>	High power – Low fluence	5W – 0.39 J/cm <sup>-2</sup>
<b>Sample 2</b>	High power – High fluence	5W – 6.95J/cm <sup>-2</sup>
<b>Sample 3</b>	Low power – Low fluence	3W – 0.23J/cm <sup>-2</sup>
<b>Sample 4</b>	Low power – High fluence	3W – 3.86J/cm <sup>-2</sup>

# Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - SEM/Raman Spectrometer Measurements



CMX850

1 $\mu$ m grain size,  
80% wt diamond content

Area 0 Initial surface

Sample 1 5W – low fluence

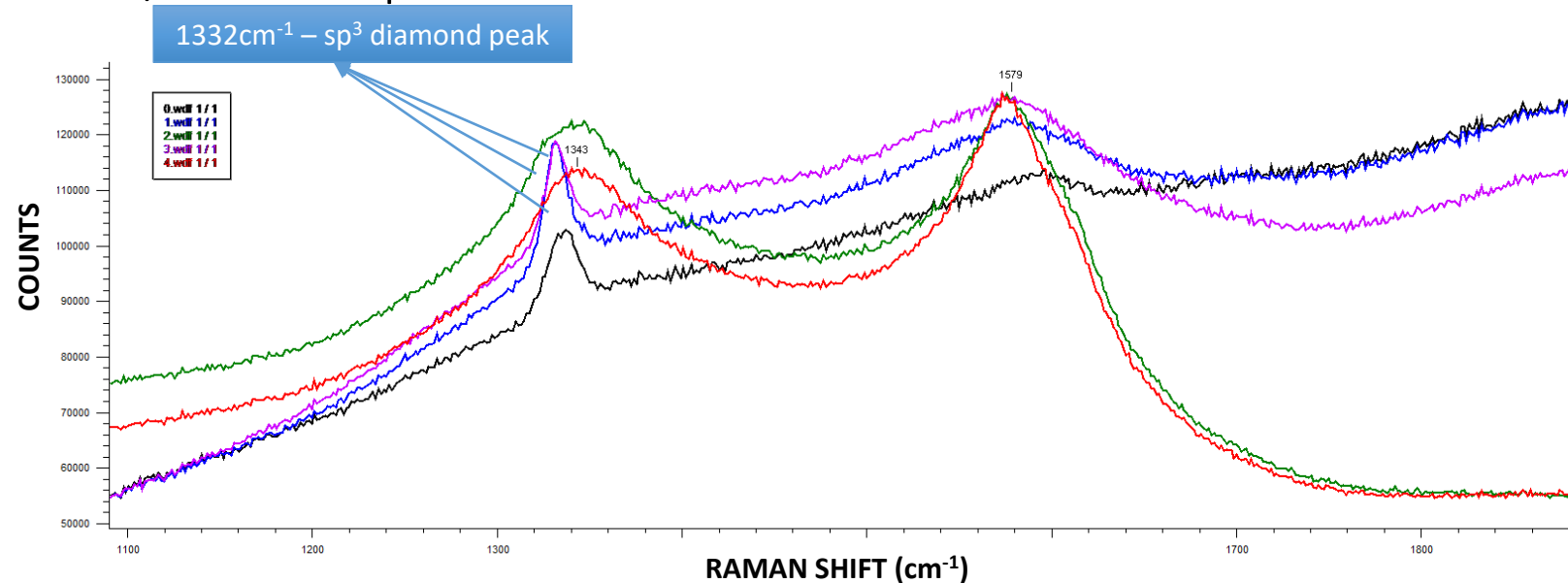
Sample 2 5W – high fluence

Sample 3 3W – low fluence

Sample 4 3W – high fluence

# Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - SEM/Raman Spectrometer Measurements



CMX850

1µm grain size,  
80% wt diamond content

Area 0 Initial surface

Sample 1 5W – low fluence

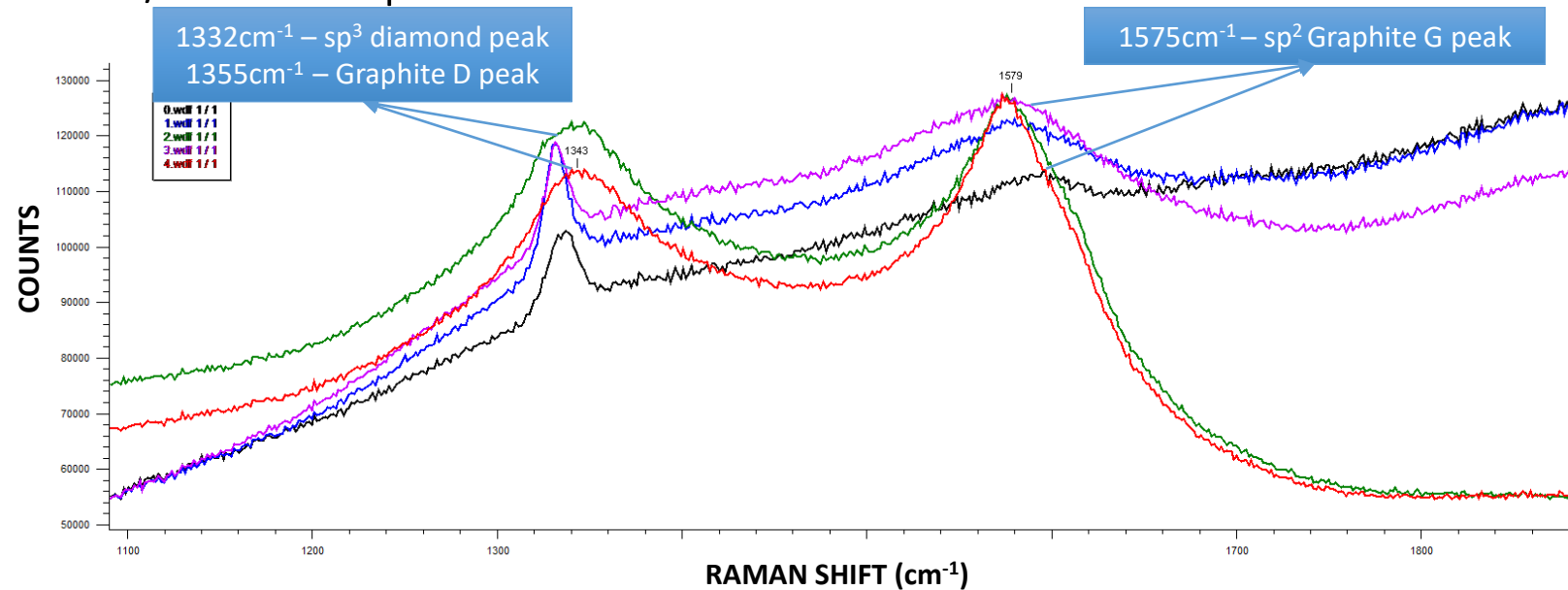
Sample 2 5W – high fluence

Sample 3 3W – low fluence

Sample 4 3W – high fluence

# Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - SEM/Raman Spectrometer Measurements



CMX850

1µm grain size,  
80% wt diamond content

Area 0 Initial surface

Sample 1 5W – low fluence

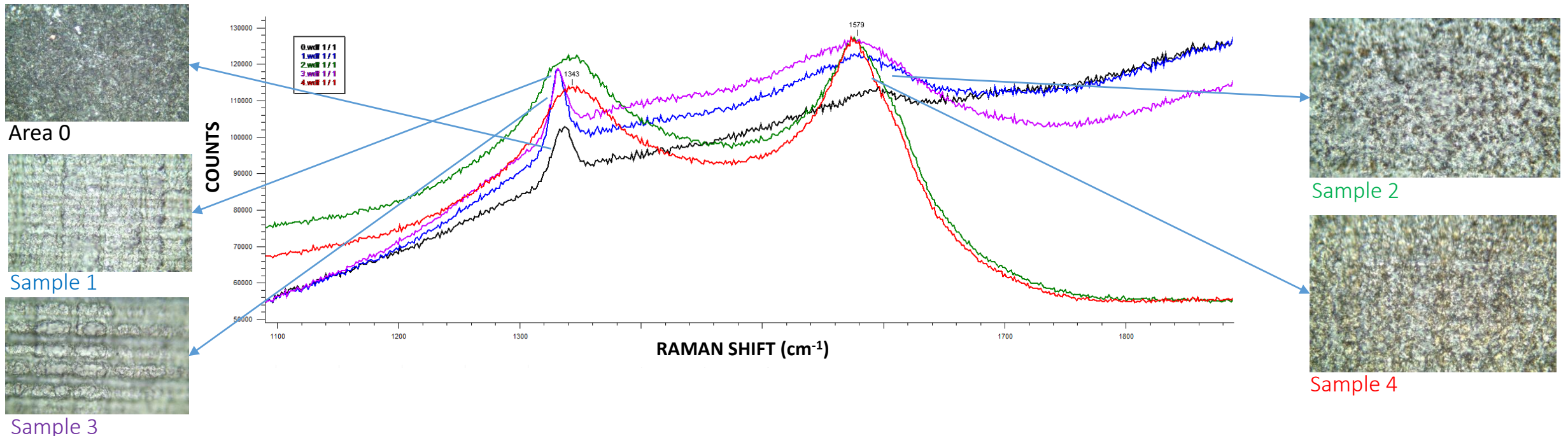
Sample 2 5W – high fluence

Sample 3 3W – low fluence

Sample 4 3W – high fluence

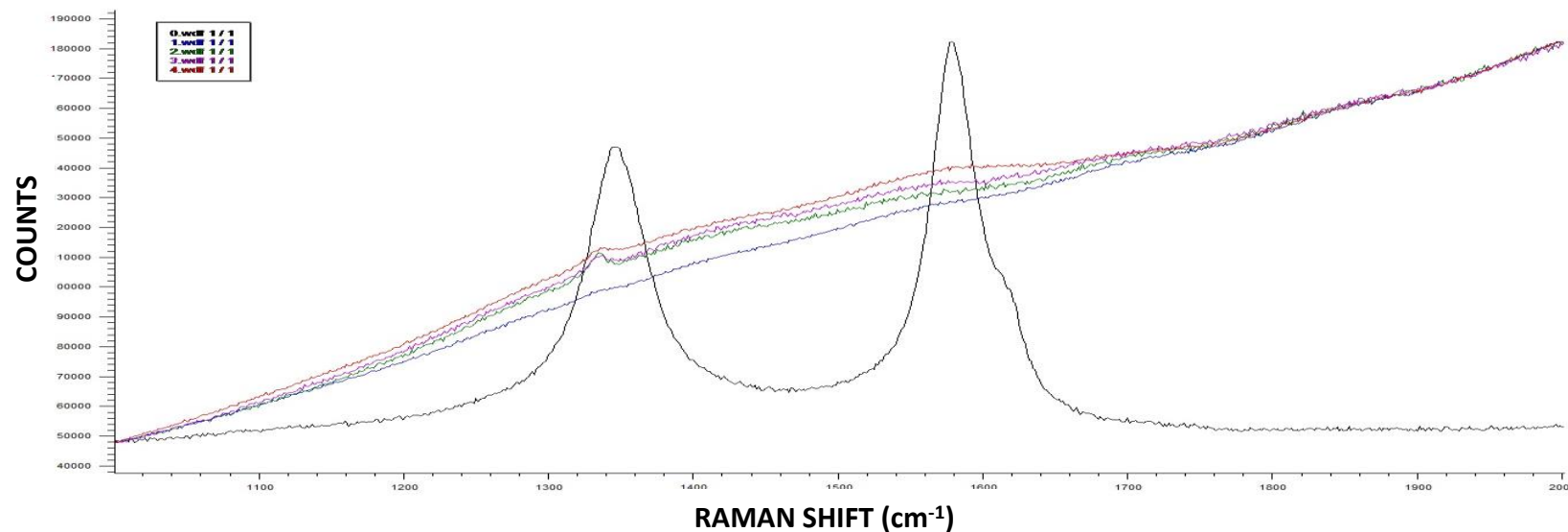
# Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - SEM/Raman Spectrometer Measurements



# Task 2.3: Fundamental process development diamond ablation

- Graphitization of Diamond under Ultra-Short Pulsed Ablation
  - SEM/Raman Spectrometer Measurements





# Task 2.3: Fundamental process development diamond ablation

- Conclusion

Parameters	Current Performances	E6 Specifications	Specification agreed with partners
Wavelength	1030nm	1030nm	1030nm (GREEN??)
Power	5W	200W	100W*
Pulse duration	230fs – 10ps	< 500 fs – 10ps	400fs – 10ps
Frequency	60kHz-1MHz	<2MHz	<2MHz
M <sup>2</sup>	1.2	1.2	<1.3
Pulse burst	None	Pulse burst	Multi pulses burst??
Maximum scanning speed	3000mm/s	<3000mm/s	3000mm/s
Spot diameter	20µm	2µm – 160µm	7.6µm - 160µm
Polarization	Circular	Circular	Circular

- \*Agreement on delivery of industrial TANGOR laser with average power of 100W
- **Installation : 14<sup>th</sup> of May**





# Task 2.4: Upscaling of applications for high throughput

- Status

- Task not started – To start by mid of June
  - Delibery of 100W TANGOR – 1st week of May
  - Installation scheduled on 14th of Mays
- D2.4 not started



# Work Package 2

- HIPERDIAS application areas:
  - 3D Silicon processing
  - Fine cutting of metals
  - Diamond ablation
- Agenda:
  - Task 2.1: Fundamentals Si Processing - Update from Bosch
  - Task 2.2: Fundamentals Fine Cutting of Metals - Update from C4L
  - Task 2.3: Fundamentals Diamond Ablation – Update from E6
  - **Task 2.4: Upscaling – Update from USTUTT**

Partners involved:



# Task 2.4: Upscaling (500 W)

- Schedule:
  - This week: Characterization of the amplified laser
  - Next week: Connecting laser to Lasea station and testing
  - Week beginning 07.05.: Start of experiments
- Goal (1000 W):

Key Performance Indicator	Symbol	Unit	Target Value	<b>BOSCH</b>
KPI #1: average ablation rate	$\bar{V}$	mm <sup>3</sup> /s	≥1	<b>0,0574</b> (P <sub>av</sub> = 20 W)
KPI #2: peak ablation rate	$\dot{V}_{max}$	mm <sup>3</sup> /s	≥3	–
KPI #3: shape deviation	$\delta_S$	µm	≤10 (waviness)	<10
KPI #4: average surface roughness	$S_a$	µm	≤1	<0,5
KPI #5: thickness of surface damage	$l_{d,sd}$	µm	≤1	<1
KPI #6: Surface defects > 1 µm	–	1/mm <sup>2</sup>	<b>none</b>	none
KPI #7: min. achievable edge radius	$r_e$	µm	≤ 200	60
KPI #8: max. edge-steepness	$\alpha_e$	degree	≥ 70	80



1.435 mm<sup>3</sup>/s  
@ 500W  
2.87 mm<sup>3</sup>/s  
@ 1000W  
(linear scaling)

# Task 2.4: Upscaling (500 W)

- Strategy:
  - Use parameters from D2.1 (Bosch) as a starting point

Laser / Process Parameters	Symbol	Unit	Value	IFS W
Average power	$P_{av}$	W	20	
Pulse duration	$\tau$	fs	320	300
Intraburst distance	$\tau_{burst}$	ns	20	25
Burst number	$n_{burst}$	-	5	Max. 5
Scan velocity	$v$	m/s	0,655	
Hatch distance	$a_{hatch}$	$\mu\text{m}$	13,1	
Pulse repetition rate	$f_{rep}$	kHz	80	Max. 1.28 MHz
Spot diameter	$d_{spot}$	$\mu\text{m}$	71,25	TBD
Pulse energy per burst	$E_{burst}$	$\mu\text{J}$	250	
Pulse energy	$E_{pulse}$	$\mu\text{J}$	50	390 $\mu\text{J}$



Number of pulses per spot:

**8,7**

Hatch overlap:

**18%**

Burst available up to **5 pulses**  
(with declining pulse energy)

Pulse repetition rate **1.28 MHz**  
(adjustable)

**D2.1:** Energy specific ablation  
volume **constant for high fluences**  
**@ 300 fs**

# Task 2.4: Upscaling (500 W)

- Strategy:
  - Investigate heat accumulation effects in detail
    - Calorimetric measurement of  $\eta_A \cdot \eta_{resP}$
    - Simulation of heat accumulation
    - Heat accumulation between pulses  $\rightarrow v_{crit} / N_{P,crit}$
    - Heat accumulation between overscans  $\rightarrow N_{OS,crit}$
  - Influence of system specific parameters on energy specific ablation volume
    - Fluence (spot size)
    - Number of burst pulses
    - Pulse repetition rate
  - Controlled ablation with OCT
    - Reach required shape accuracy by controlled depth progress
    - Two step process possible: Fast ablation followed by accuracy improvement.